



MPQ4347/4347J

36V, 4A, Ultra-Low Quiescent Current, Synchronous Step-Down Converter, AEC-Q100 Qualified

DESCRIPTION

The MPQ4347/4347J is a configurable-frequency (350kHz to 2.5MHz), synchronous, step-down switching regulator with an integrated internal high-side and low-side MOSFET (HS-FET and LS-FET, respectively). The device provides 4A of highly efficient output current (I_{OUT}) with fixed-frequency, zero-delay pulse-width modulation (PWM) control to optimize transient response.

The wide 3.3V to 36V input voltage (V_{IN}) range with 42V load dump support accommodates a variety of step-down applications in an automotive input environment. The 1 μ A shutdown mode quiescent current allows the device to be used in battery-powered applications.

High power conversion efficiency across the wide load range is achieved by scaling down the switching frequency (f_{SW}) under light-load conditions to reduce the switching and gate driving losses.

An open-drain power good (PG) signal indicates whether the output is within 94% to 106% of its nominal voltage.

Thermal shutdown provides reliable, fault-tolerant operation. A high duty cycle and low-dropout mode are provided for automotive cold-crank conditions.

The MPQ4347 is available in a QFN-17 (3mmx4mm) package. The MPQ4347J is available in a QFN-19 (3mmx4mm) package with wettable flanks.

FEATURES

- Designed for Automotive Applications:
 - Survives 42V Load Dump
 - Supports 3.1V Cold Crank
 - Low-Dropout (LDO) Mode
 - 4A Continuous Output Current (I_{OUT})
 - Continuous Operation Up to 36V
 - Zero-Delay Pulse-Width Modulation (PWM) Control
 - 20ns Minimum On Time

- Junction Temperature Operation from -40°C to +150°C
- Available in AEC-Q100 Grade 1
- Increases Battery Life:
 - 1 μ A Low Shutdown Supply Current
 - 3 μ A Sleep Mode Quiescent Current (I_Q)
 - AAM Mode Increases Efficiency Under Light Loads
- High Performance for Improved Thermals:
 - Internal 60m Ω High-Side MOSFET and 35m Ω Low-Side MOSFET
- Optimized for EMC/EMI:
 - Configurable 350kHz to 2.5MHz Switching Frequency (f_{SW})
 - Symmetric VIN Pinout
 - Frequency Spread Spectrum Modulation
 - CISPR25 Class 5 Compliant
 - MeshConnect™ Flip-Chip Package
- Additional Features:
 - Fixed Output Options ⁽¹⁾: 1V, 1.1V, 1.8V, 2.5V, 3.0V, 3.3V, 3.7V, 3.8V, 5V
 - Power Good (PG) Output
 - Synchronize to External Clock
 - Synchronized to Clock Output
 - External Soft Start
 - Over-Current Protection (OCP) with Hiccup Mode
 - Available in a QFN-17 (3mmx4mm) Package (MPQ4347)
 - Available in a QFN-19 (3mmx4mm) Package with Wettable Flanks (MPQ4347J)

APPLICATIONS

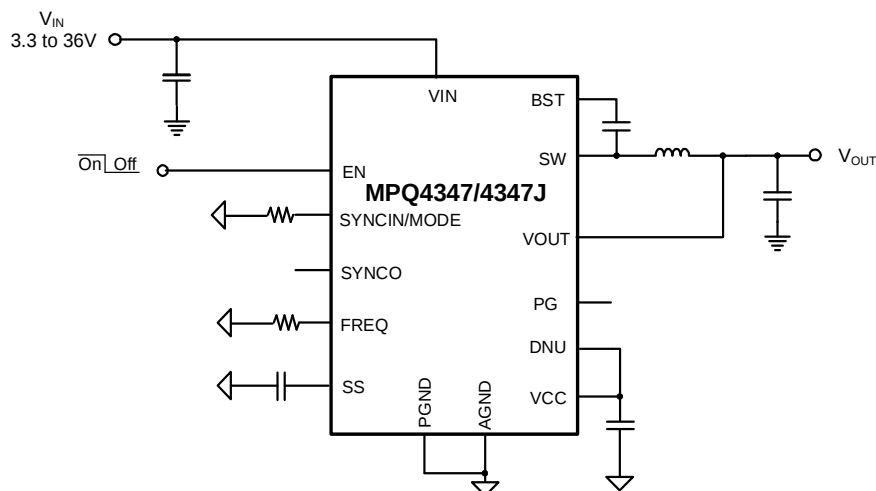
- Automotive Clusters
- Automotive Infotainment
- Advanced Driver Assistance Systems (ADAS)
- Industrial Power Systems

All MPS parts are lead-free, halogen-free, and adhere to the RoHS directive. For MPS green status, please visit the MPS website under Quality Assurance. "MPS", the MPS logo, and "Simple, Easy Solutions" are trademarks of Monolithic Power Systems, Inc. or its subsidiaries.

Note:

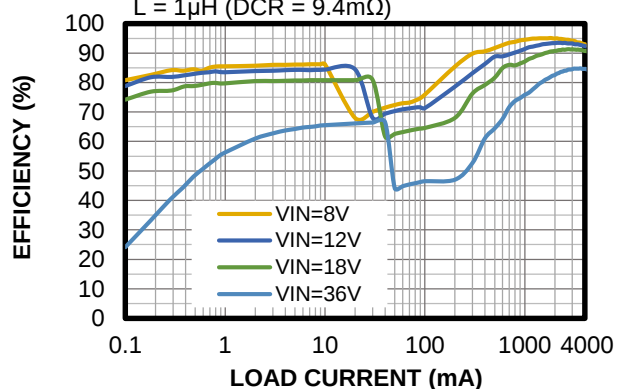
- See the Ordering Information section on page 3 for the exact availability of each fixed output version. Additional output voltages may be available. Contact MPS for details.

TYPICAL APPLICATION



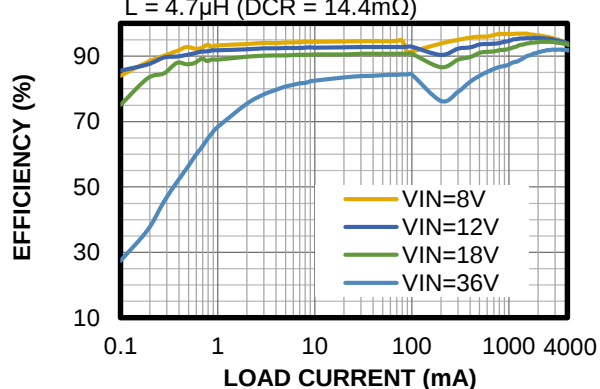
Efficiency vs. Load Current

AAM, $V_{OUT} = 5V$, $f_{SW} = 2.2MHz$,
 $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$,
 $L = 1\mu H$ (DCR = 9.4m Ω)



Efficiency vs. Load Current

AAM, $V_{OUT} = 5V$, $f_{SW} = 410kHz$,
 $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$,
 $L = 4.7\mu H$ (DCR = 14.4m Ω)



ORDERING INFORMATION

Part Number* (2)	Output Voltage	Package	Top Marking	MSL Rating**
MPQ4347GLE-33-AEC1***	Fixed 3.3V	QFN-17 (3mmx4mm)	See Below	1
MPQ4347GLE-37-AEC1***	Fixed 3.7V	QFN-17 (3mmx4mm)	See Below	1
MPQ4347GLE-5-AEC1***	Fixed 5V	QFN-17 (3mmx4mm)	See Below	1
MPQ4347JGLE-33-AEC1***	Fixed 3.3V	QFN-19 (3mmx4mm)	See Below	1
MPQ4347JGLE-5-AEC1***	Fixed 5V	QFN-19 (3mmx4mm)	See Below	1

* For Tape & Reel, add suffix -Z (e.g. MPQ4347GLE-33-AEC1-Z).

**Moisture Sensitivity Level Rating

*** Wettable Flank

Note:

2) Contact MPS for the details regarding the other fixed output versions.

TOP MARKING

(MPQ4347GLE-33-AEC1, MPQ4347GLE-37-AEC1 and MPQ4347GLE-5-AEC1)

MPYW
4347
LLL
E

MP: MPS prefix
Y: Year code
W: Week code
4347: Part number
LLL: Lot number
E: Wettable flank

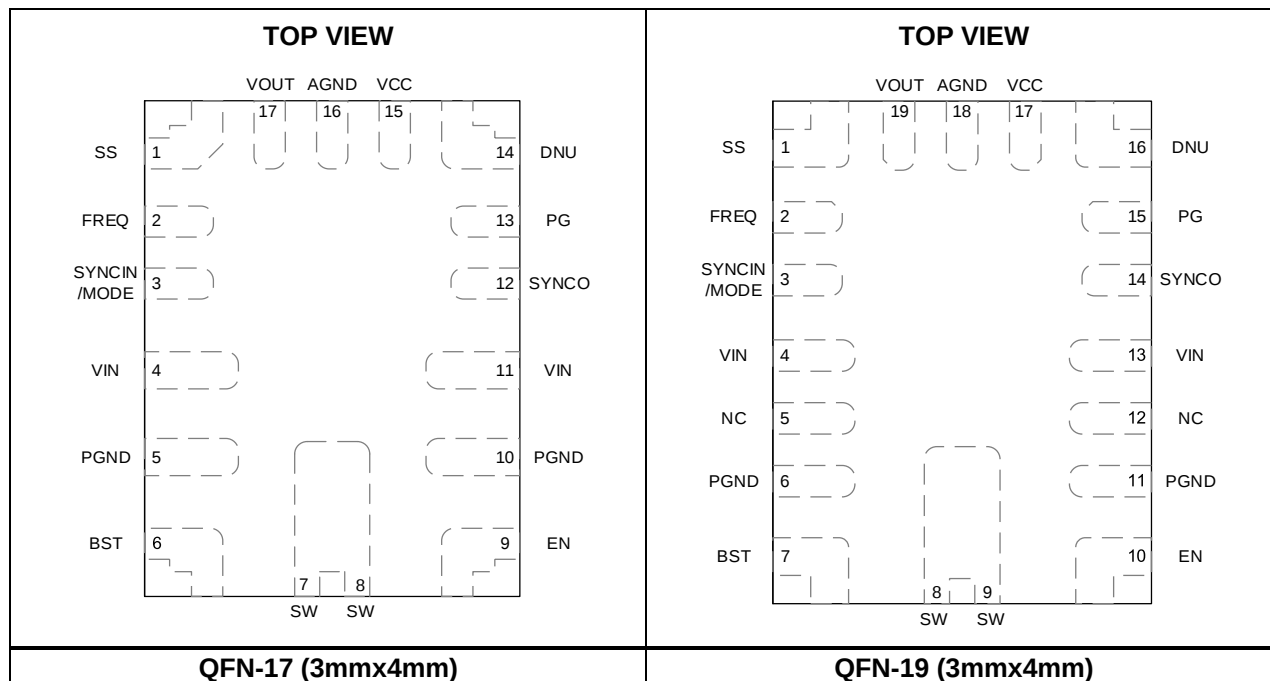
TOP MARKING

(MPQ4347JGLE-33-AEC1 and MPQ4347JGLE-5-AEC1)

MPYW
4347
JLLL
E

MP: MPS prefix
Y: Year code
W: Week code
4347J: Part number
LLL: Lot number
E: Wettable flank

PACKAGE REFERENCE



PIN FUNCTIONS

Pin # QFN-19	Pin # QFN-17	Name	Description
1	1	SS	Soft start input. Place a capacitor from the SS pin to GND to set the soft-start period. The MPQ4347/4347J sources 10μA from SS to the soft-start capacitor at start-up. As the SS voltage (V _{SS}) rises, the feedback reference voltage (V _{REF}) increases to limit inrush current during start-up. Do not float this pin.
2	2	FREQ	Switching frequency configuration. Connect a resistor from the FREQ pin to ground to set the switching frequency (f _{sw}).
3	3	SYNCIN/ MODE	SYNC input and MODE selection. Apply a clock signal to the SYNCIN/MODE pin to synchronize the internal oscillator frequency to the external clock. Use an external clock or pull this pin high to enter forced continuous conduction mode (FCCM). Pull this pin low to enable advanced asynchronous modulation (AAM) mode and pulse-skipping under light loads. Do not float this pin.
4, 13	4, 11	VIN	Input supply. The VIN pin supplies power to all of the internal control circuitry, as well as the power switch connected to SW. Place a decoupling capacitor from VIN to ground to minimize switching spikes. The capacitor should be close to VIN.
5, 12	-	NC	No connection. Float the NC pin.
6, 11	5, 10	PGND	Power ground.
7	6	BST	Bootstrap. The BST pin is the positive power supply for the high-side MOSFET (HS-FET) connected to SW. Connect a bypass capacitor between the BST and SW pin. See the Bootstrap Charging (BST, Pin 6) section on page 42 to calculate the size of this capacitor.
8, 9	7, 8	SW	Switch node. The SW pin is the output of the internal power switch.
10	9	EN	Enable. Pull the EN pin below the specified threshold (0.85V) to shut the chip down. Pull EN above the specified threshold (1V) to enable the chip. Do not float this pin.
14	12	SYNCO	SYNC output. The SYNCO pin outputs a clock signal in phase with the internal oscillator signal, or the clock signal applied at the SYNCIN/MODE pin. This pin can be floated.
15	13	PG	Power good output. The output of the PG pin is an open drain. If PG is used, it should be connected to a power source with a pull-up resistor. PG goes high if the output voltage is within 94% to 106% of the nominal voltage. PG goes low if the output voltage is above 107% or below 93% of the nominal voltage. Float this pin if not used.
16	14	DNU	Do Not Use. Connect the DNU pin directly to VCC.
17	15	VCC	Bias supply. The VCC pin supplies 5V to power the internal control circuit and gate drivers. Place a decoupling capacitor from this pin to ground, and close to this pin. See the Setting the VCC Capacitor (VCC, Pin 15) section on page 44 to calculate the size of this capacitor.
18	16	AGND	Analog ground.
19	17	VOUT	V_{OUT} regulation point. Connect the VOUT pin directly to the output voltage.

ABSOLUTE MAXIMUM RATINGS ⁽³⁾

VIN, EN.....	-0.3V to +42V
SW.....	-0.3V to V _{IN(MAX)} + 0.3V
BST.....	V _{SW} + 5.5V
All other pins.....	-0.3V to +6V
Continuous power dissipation (T _A = 25°C)	
QFN-17 (3mmx4mm) ^{(4) (8)}	4.28W
QFN-19 (3mmx4mm) ^{(4) (8)}	4.13W
Junction temperature.....	150°C
Lead temperature.....	260°C
Storage temperature.....	-65°C to +150°C

Electrostatic Discharge (ESD) Ratings

Human body model (HBM)	Class 2 ⁽⁵⁾
Charged device model (CDM).....	Class C2b ⁽⁶⁾

Recommended Operating Conditions

Supply voltage (V _{IN})	3.3V to 36V
Operating junction temp (T _J).....	-40°C to +150°C

Thermal Resistance

QFN-17 (3mmx4mm)	θ_{JA}	θ_{JC}	
JESD51-7.....	44.7	5.2	°C/W ⁽⁷⁾
EVQ4347-L-00A.....	29.2		°C/W ⁽⁸⁾
		Ψ_{JT}	
JESD51-7.....		1.2	°C/W ⁽⁷⁾
EVQ4347-L-00A.....		6.1	°C/W ⁽⁸⁾
QFN-19 (3mmx4mm)	θ_{JA}	θ_{JC}	
JESD51-7.....	43.6	5.4	°C/W ⁽⁷⁾
EVQ4347J-L-00A	30.3		°C/W ⁽⁸⁾
		Ψ_{JT}	
JESD51-7.....		0.9	°C/W ⁽⁷⁾
EVQ4347J-L-00A.....		5.17	°C/W ⁽⁸⁾

Notes:

- 3) Exceeding these ratings may damage the device.
- 4) The maximum allowable power dissipation is a function of the maximum junction temperature, T_J (MAX), the junction-to-ambient thermal resistance, θ_{JA} , and the ambient temperature, T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P_D (MAX) = (T_J (MAX) - T_A) / θ_{JA} . Exceeding the maximum allowable power dissipation can cause excessive die temperature, and the regulator may go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- 5) Per AEC-Q100-002.
- 6) Per AEC-Q100-011.
- 7) Measured on JESD51-7, 4-layer PCB. The values given in this table are only valid for comparison with other packages and cannot be used for design purposes. These values were calculated in accordance with JESD51-7, and simulated on a specified JEDEC board. They do not represent the performance obtained in an actual application. The value of θ_{JC} shows the thermal resistance from junction-to-case bottom. The value of Ψ_{JT} shows the characterization parameter from junction-to-case top
- 8) Measured on an MPS standard EVB: 8.3cmx8.3cm, 2oz. copper thickness, 4-layer PCB, and the value of Ψ_{JT} shows the characterization parameter from junction-to-case top.

ELECTRICAL CHARACTERISTICS

V_{IN} = 12V, V_{EN} = 2V, T_J = -40°C to +150°C, unless otherwise note, typical values are at T_J = 25°C.

Parameter	Symbol	Condition	Min	Typ	Max	Units
Input Supply						
Minimum operating input voltage (V _{IN})	V _{IN_MIN}				3.3	V
V _{IN} under-voltage lockout (UVLO) rising threshold	V _{INUVLO_RISING}		2.8	3	3.2	V
V _{IN} UVLO falling threshold	V _{INUVLO_FALLING}		2.6	2.8	3	V
V _{IN} UVLO hysteresis	V _{INUVLO_HYS}			200		mV
V _{IN} quiescent current ⁽⁹⁾	I _Q	V _{OUT} = 1.05 x V _{SET} , no load, (sleep mode), T _J = -40°C to +85°C	1.9	3	3.6	μA
		V _{OUT} = 1.05 x V _{SET} , no load, (sleep mode), T _J = -40°C to +125°C	1.5		15	μA
V _{IN} quiescent current (switching) ⁽⁹⁾	I _{Q_SLEEP}	SYNCIN/MODE = GND (AAM mode), switching, no load, T _J = -40°C to +85°C	2.4	3.5	4.5	μA
		SYNCIN/MODE = GND (AAM mode), switching, no load, T _J = -40°C to +125°C	2		16	μA
V _{IN} active current (no-switching)	I _{Q_ACTIVE}	SYNCIN/MODE = V _{CC} (FCCM), no switching		1200		μA
V _{IN} shutdown current	I _{SHDN}	EN = 0V, T _J = 25°C		1	3	μA
		EN = 0V			11	μA
V _{IN} over-voltage protection (OVP) threshold	V _{INOVP_RISING}		36	38	40	V
V _{IN} OVP hysteresis	V _{INOVP_HYS}			10		V
EN						
EN rising threshold	V _{EN_RISING}		0.8	1	1.2	V
EN falling threshold	V _{EN_FALLING}		0.65	0.85	1.05	V
EN hysteresis voltage	V _{EN_HYS}			150		mV
Switches and Frequency						
Switching frequency	f _{SW}	R _{FREQ} = 86.6kΩ	370	410	450	kHz
		R _{FREQ} = 33kΩ	950	1050	1150	kHz
		R _{FREQ} = 15kΩ	1980	2200	2420	kHz
Minimum on time	t _{ON_MIN}			20	35	ns
Minimum off time	t _{OFF_MIN}			120	140	ns
Switch leakage current	I _{SW_LKG}			0.01	5	μA
High-side (HS) switch on resistance	R _{ON_HS}	V _{BST} - V _{SW} = 5V		60	110	mΩ
Low-side (LS) switch on resistance	R _{ON_LS}	V _{CC} = 5V		35	60	mΩ

ELECTRICAL CHARACTERISTICS (continued)

V_{IN} = 12V, V_{EN} = 2V, T_J = -40°C to +150°C, unless otherwise note, typical values are at T_J = 25°C.

Parameter	Symbol	Condition	Min	Typ	Max	Units
BST						
BST-SW refresh rising threshold	V _{BST-SW_RISNG}			2.5	2.9	V
BST-SW refresh falling threshold	V _{BST-SW_FALING}			2.3	2.7	V
BST-SW refresh hysteresis	V _{BST-SW_HYS}			0.2		V
Soft Start and VCC						
VCC voltage	V _{CC}	I _{VCC} = 0mA	4.7	5	5.3	V
VCC regulation		I _{VCC} = 0mA and 30mA			1	%
VCC current limit	I _{LIMIT_VCC}	V _{CC} = 4V	50	100		mA
		V _{CC} = 0V		70		mA
Soft-start current	I _{SS}	V _{SS} = 0V		10		μA
Output and Regulation						
Output voltage accuracy of 3.3V fixed output version	V _{OUT_ACC_3.3}	T _J = 25°C	3260	3300	3340	mV
		T _J = -40°C to +150°C	3230	3300	3370	mV
Output voltage accuracy of 3.7V fixed output version	V _{OUT_ACC_3.7}	T _J = 25°C	3650	3700	3750	mV
		T _J = -40°C to +150°C	3620	3700	3780	mV
Output voltage accuracy of 5V fixed output version	V _{OUT_ACC_5}	T _J = 25°C	4940	5000	5060	mV
		T _J = -40°C to +150°C	4900	5000	5100	mV
V _{OUT} current	I _{VOUT}	V _{OUT} = V _{OUT_REG}		300		nA
V _{OUT} discharge	I _{DISCHARGE}	EN = 0V, V _{OUT} = 0.3V, V _{IN} = 3.3V to 36V	1.8			mA
PG						
PG rising threshold	PG _{VTH_RISING}	V _{OUT} rising	91	94	97	%
		V _{OUT} falling	103	106	109	
PG falling threshold	PG _{VTH_FALLING}	V _{OUT} falling	90	93	96	%
		V _{OUT} rising	104	107	110	
PG trip threshold hysteresis	PG _{VTH_HYS}			1		%
PG output voltage low	V _{PG_LOW}	I _{SINK} = 1mA		0.1	0.3	V
PG rising deglitch time	t _{PG_R}			50		μs
PG falling deglitch time	t _{PG_F}			50		μs
SYNCIN and SYNCO						
SYNCIN/MODE voltage rising threshold	V _{SYNC_RISING}		1.8			V
SYNCIN/MODE voltage falling threshold	V _{SYNC_FALLING}				0.4	V
SYNCIN/MODE timeout	t _{MODE}	SYNCIN/MODE low to AAM mode		41		μs
SYNCIN clock range	f _{SYNC}	% of free-running frequency	90		115	%
SYNCO high voltage	V _{SYNCO_HIGH}	I _{SYNCO} = -1mA	3.3	5		V
SYNCO low voltage	V _{SYNCO_LOW}	I _{SYNCO} = 1mA			0.4	V

ELECTRICAL CHARACTERISTICS (continued)

V_{IN} = 12V, V_{EN} = 2V, T_J = -40°C to +150°C, unless otherwise note, typical values are at T_J = 25°C.

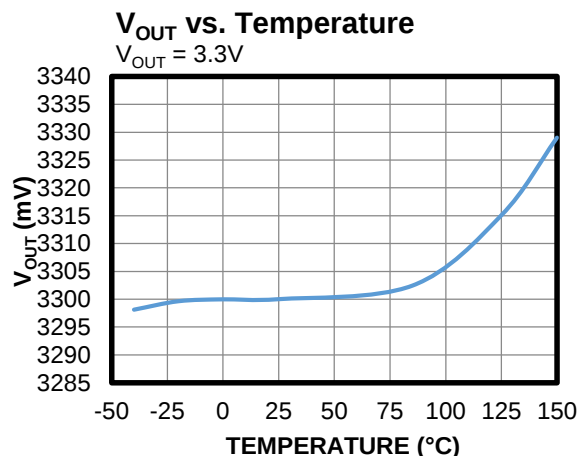
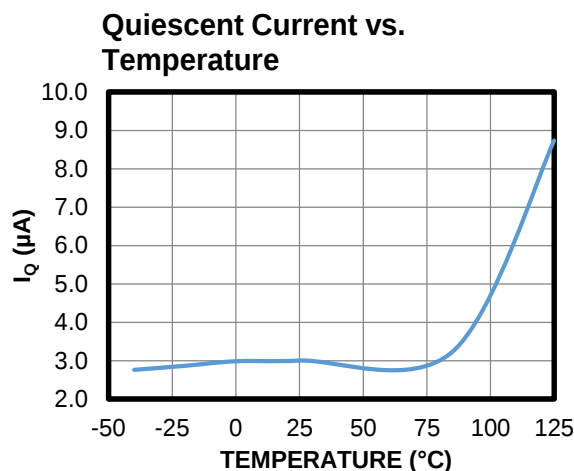
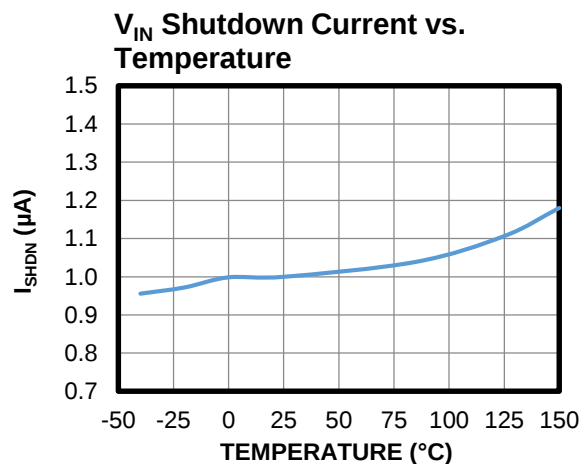
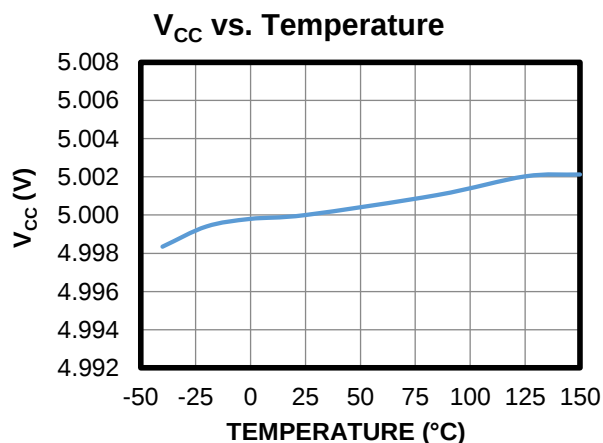
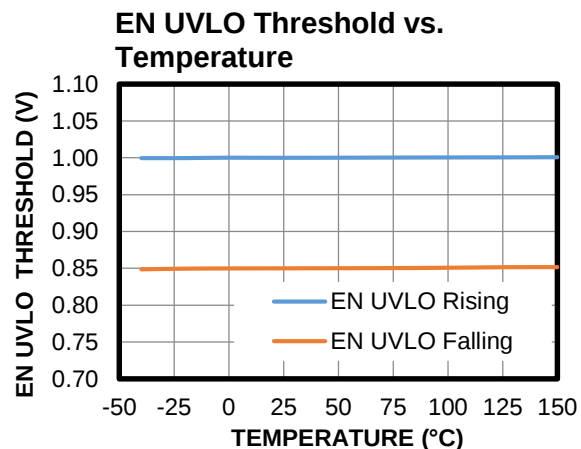
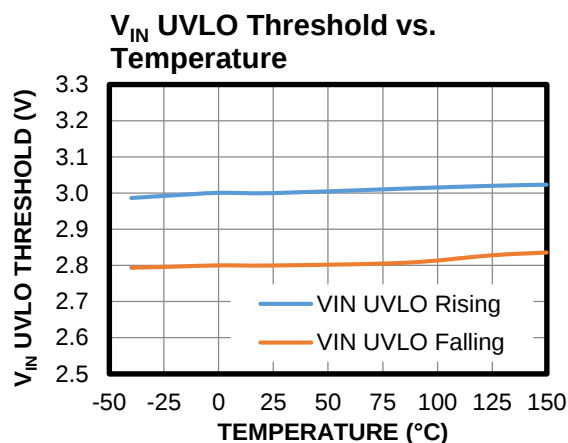
Parameter	Symbol	Condition	Min	Typ	Max	Units
Protections						
HS current limit	I _{LIMIT_HS}	Duty cycle = 30%	6.3	7.7	9.7	A
LS valley current limit ⁽⁹⁾	I _{LIMIT_LS}		4.1	5.9	7.6	A
Zero-current detection (ZCD) current	I _{ZCD}	AAM mode	-0.05	+0.1	+0.25	A
LS reverse current limit	I _{LIMIT_REVERSE}	FCCM		4		A
Thermal shutdown ⁽⁹⁾	T _{SD}		150	170		°C
Thermal shutdown hysteresis ⁽⁹⁾	T _{SD_HYS}			20		°C

Note:

9) Guaranteed by design and characterization. Not tested in production.

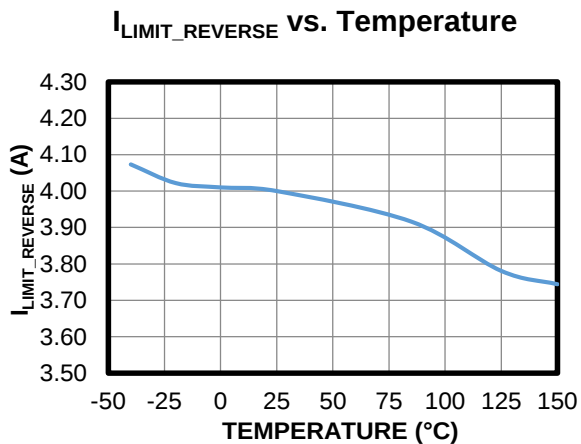
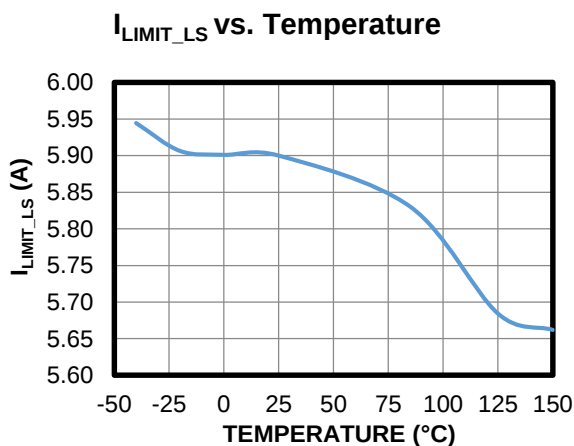
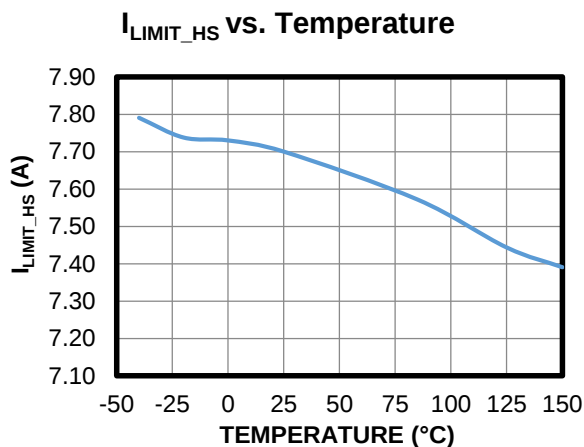
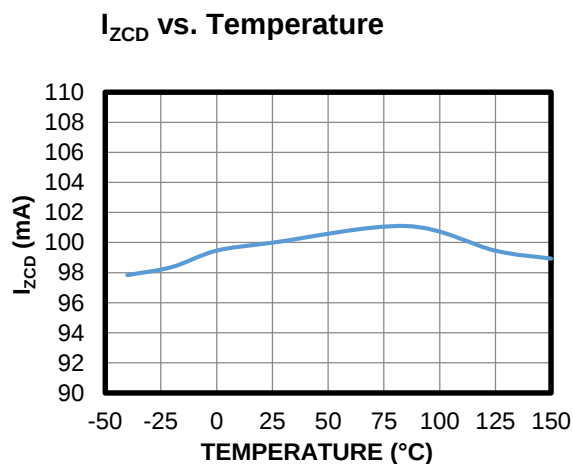
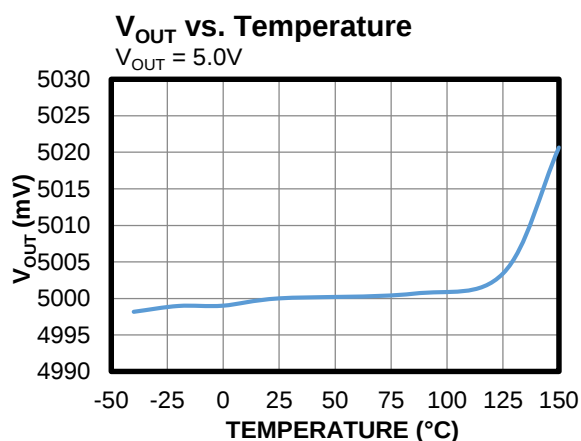
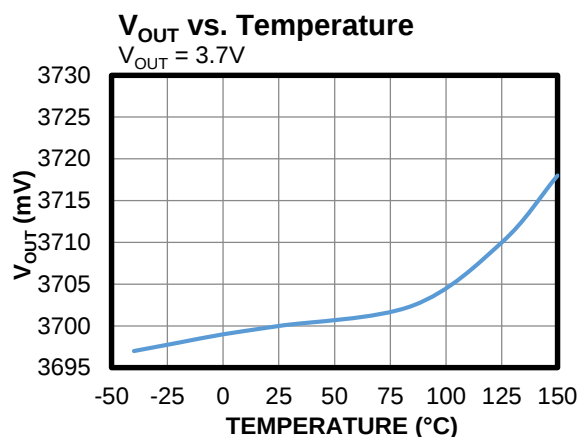
TYPICAL PERFORMANCE CHARACTERISTICS

$V_{IN} = 12V$, $T_J = -40^{\circ}C$ to $+150^{\circ}C$, unless otherwise noted.



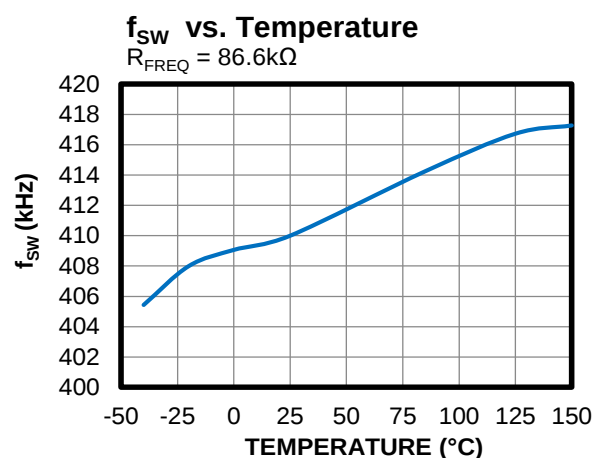
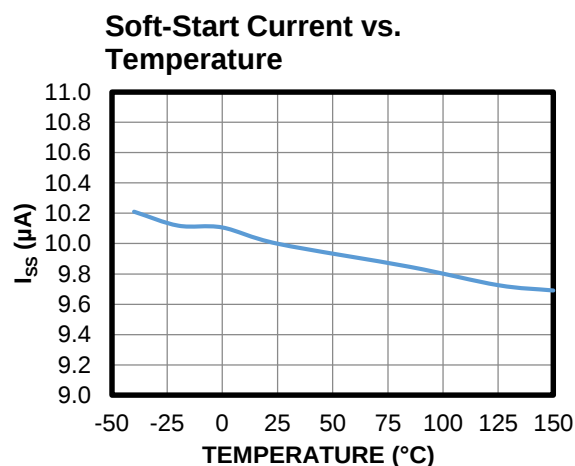
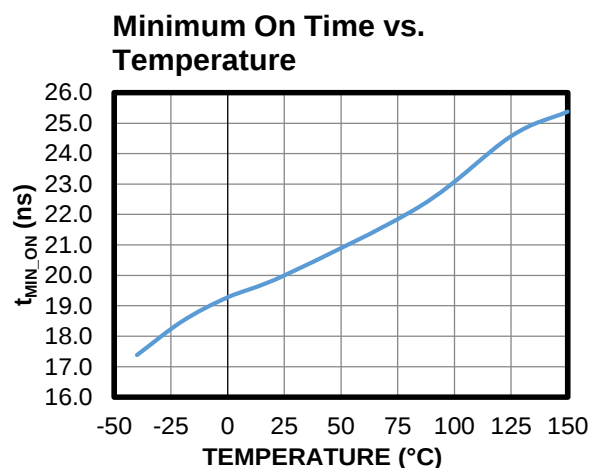
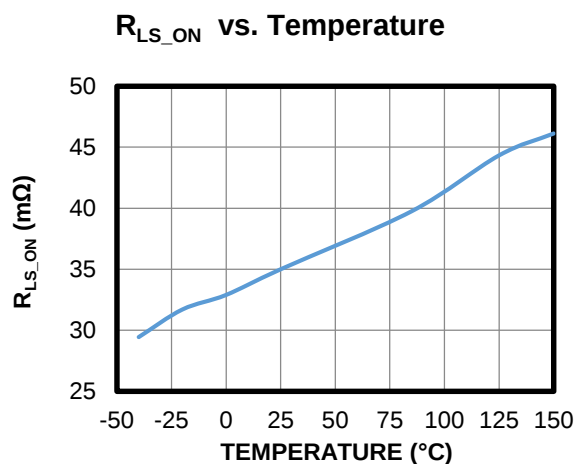
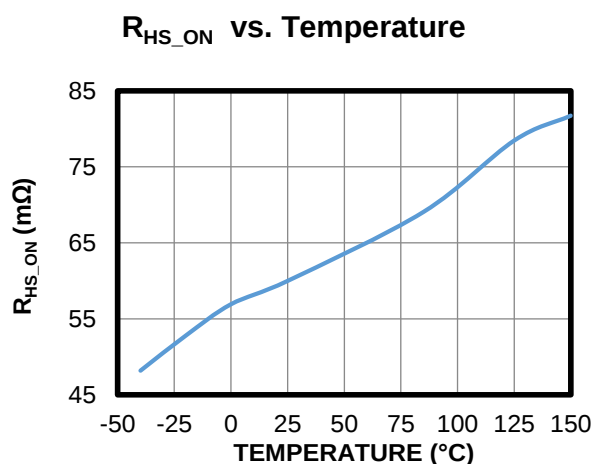
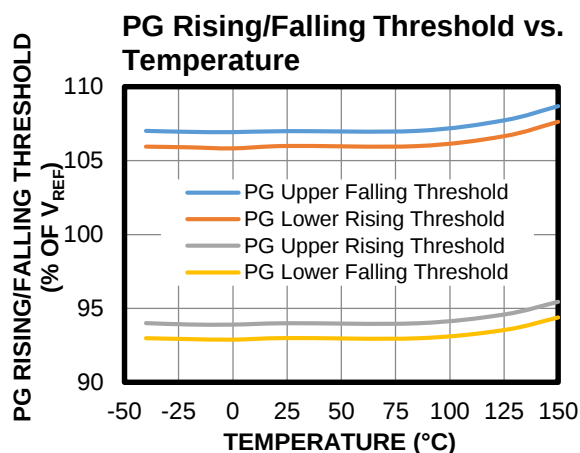
TYPICAL CHARACTERISTICS (continued)

$V_{IN} = 12V$, $T_J = -40^{\circ}C$ to $+150^{\circ}C$, unless otherwise noted.



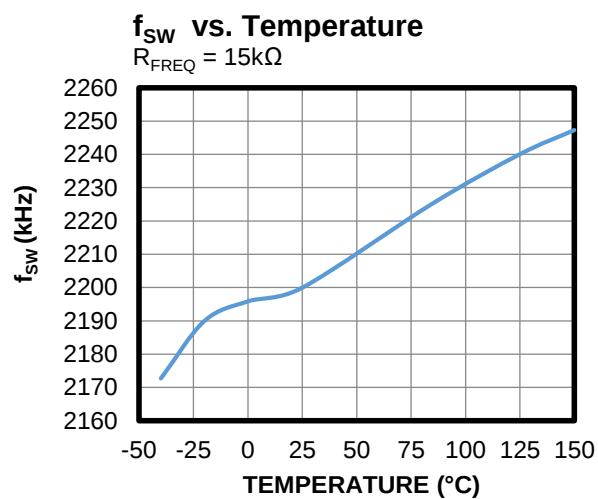
TYPICAL CHARACTERISTICS (continued)

$V_{IN} = 12V$, $T_J = -40^{\circ}C$ to $+150^{\circ}C$, unless otherwise noted.



TYPICAL CHARACTERISTICS *(continued)*

$V_{IN} = 12V$, $T_J = -40^{\circ}C$ to $+150^{\circ}C$, unless otherwise noted.

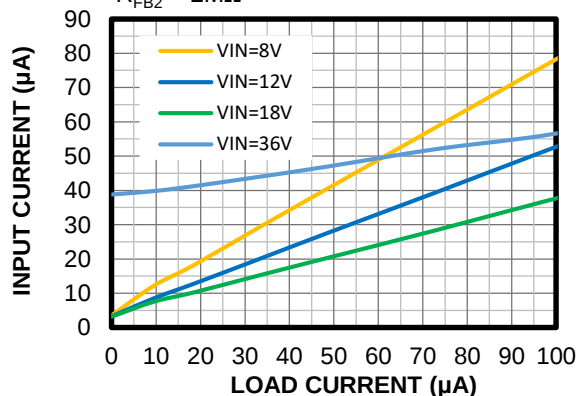


TYPICAL PERFORMANCE CHARACTERISTICS

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$ (DCR = $9.4m\Omega$), $f_{SW} = 2.2MHz$, $T_A = 25^\circ C$, unless otherwise noted.

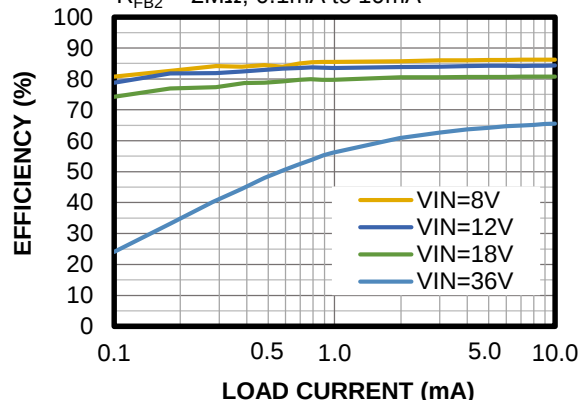
Input Current vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$



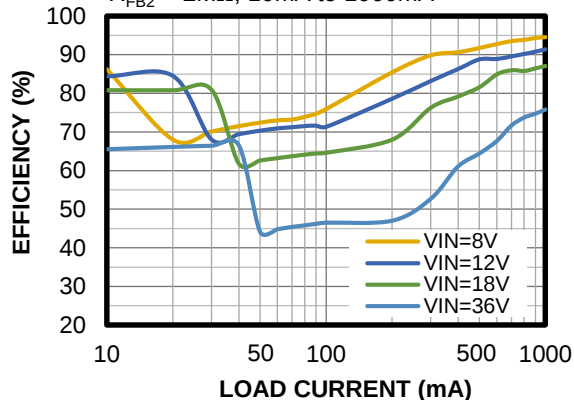
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$, 0.1mA to 10mA



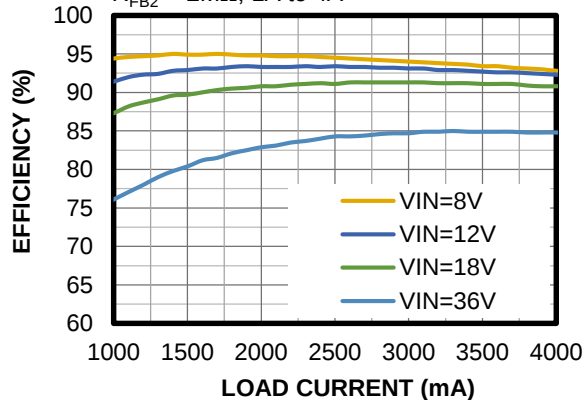
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$, 10mA to 1000mA



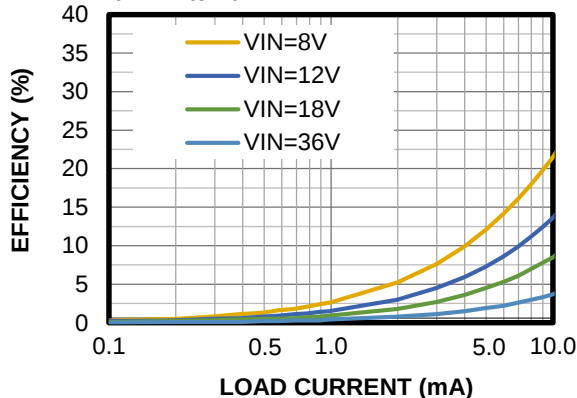
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$, 1A to 4A



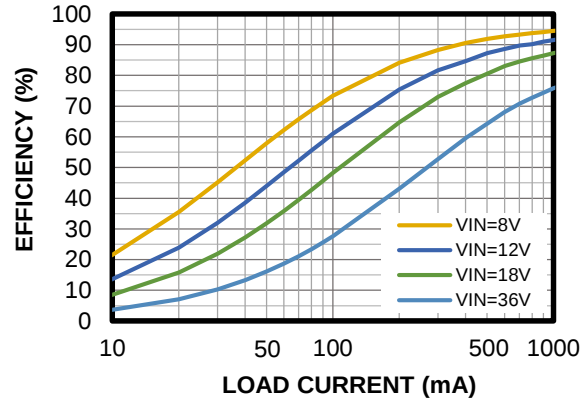
Efficiency vs. Load Current

FCCM, $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$,
0.1mA to 10mA



Efficiency vs. Load Current

FCCM, $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$,
10mA to 1000mA

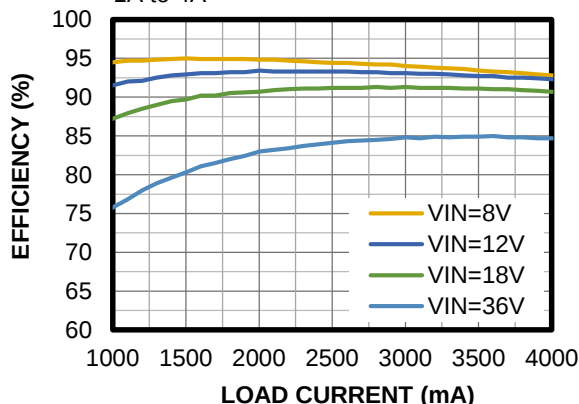


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$ (DCR = $9.4m\Omega$), $f_{SW} = 2.2MHz$, $T_A = 25^\circ C$, unless otherwise noted.

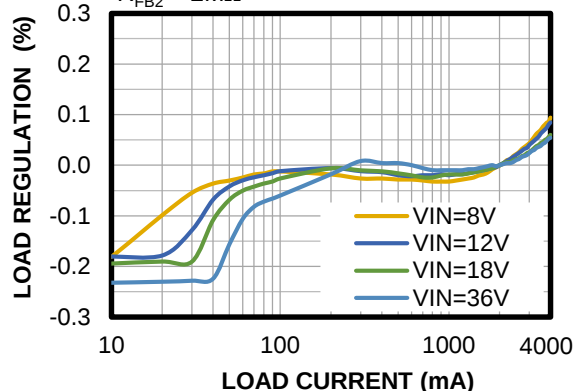
Efficiency vs. Load Current

FCCM, $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$,
1A to 4A



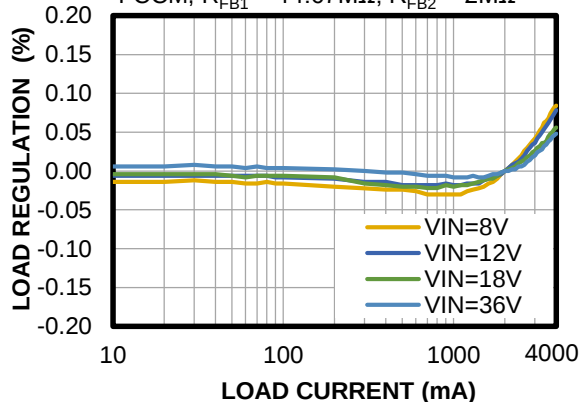
Load Regulation vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$



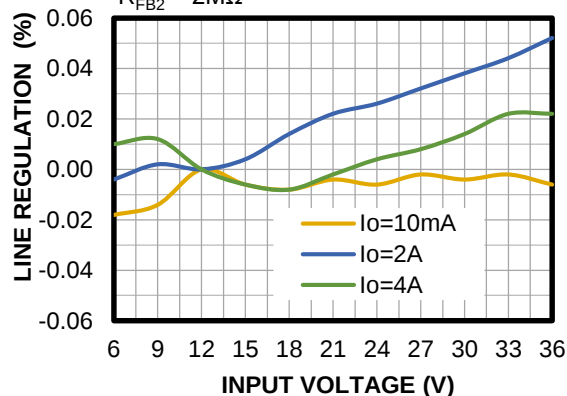
Load Regulation vs. Load Current

FCCM, $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$



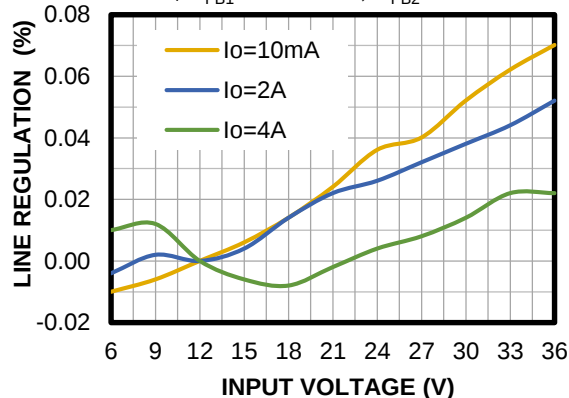
Line Regulation vs. Input Voltage

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$



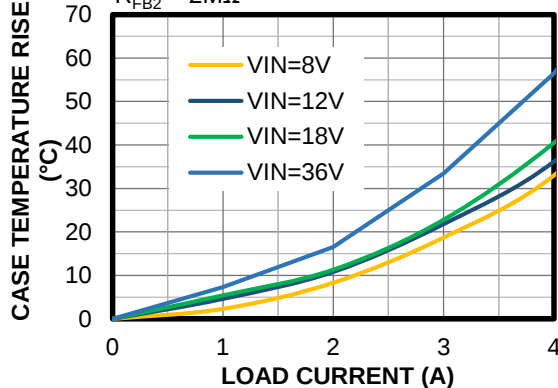
Line Regulation vs. Input Voltage

FCCM, $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$



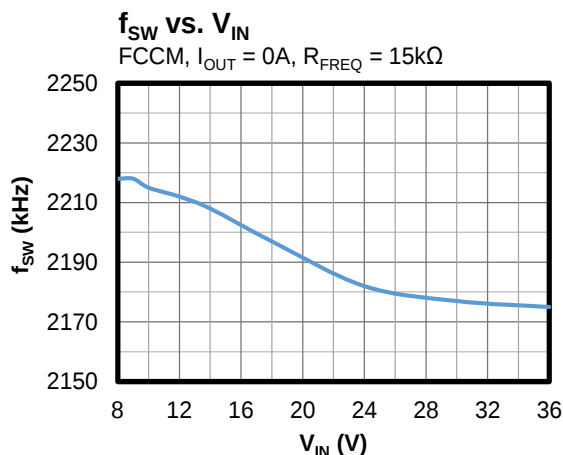
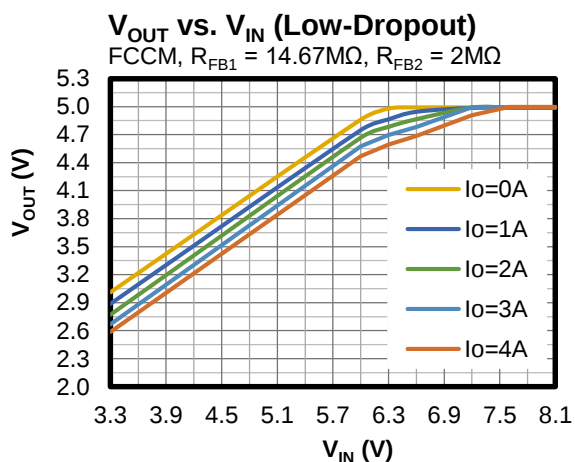
Case Temperature Rise vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$ (DCR = $9.4m\Omega$), $f_{SW} = 2.2MHz$, $T_A = 25^\circ C$, unless otherwise noted.

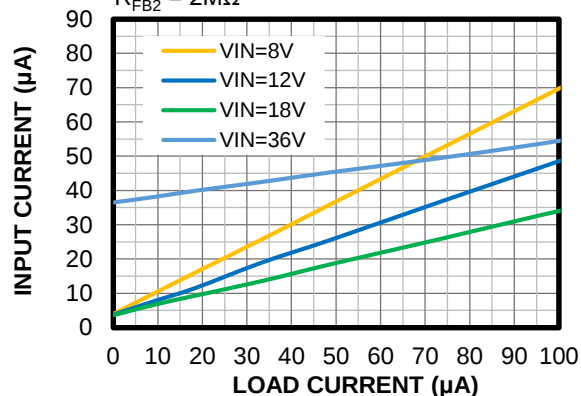


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 4.7\mu H$ (DCR = 14.4m Ω), $f_{SW} = 410kHz$, $T_A = 25^\circ C$, unless otherwise noted.

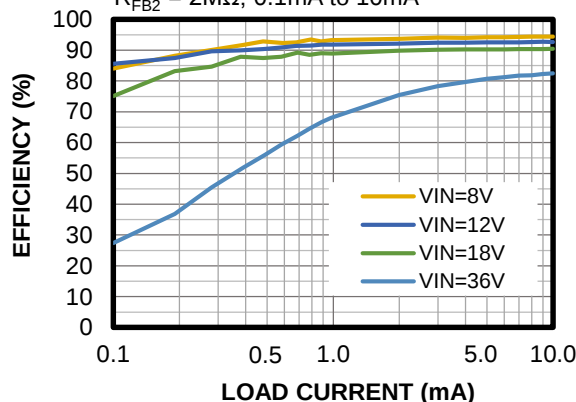
Input Current vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$



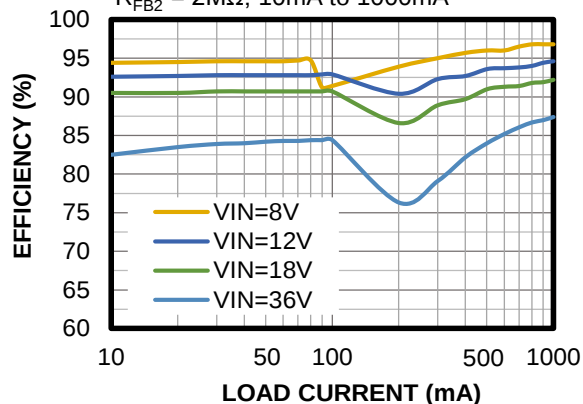
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$, 0.1mA to 10mA



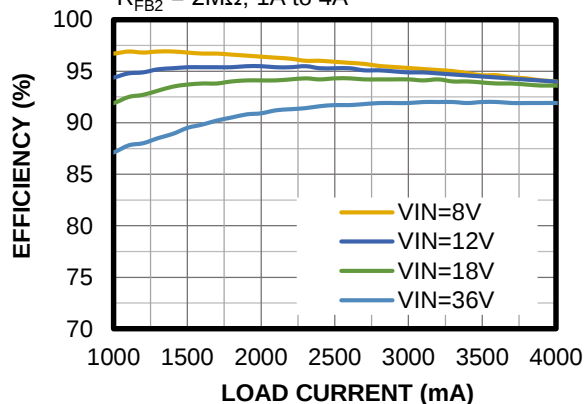
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$, 10mA to 1000mA



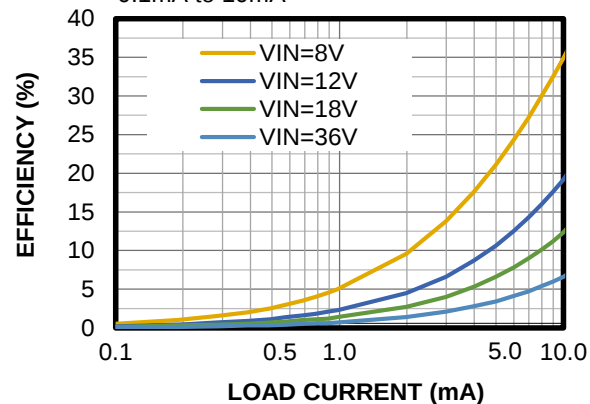
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 14.67M\Omega$,
 $R_{FB2} = 2M\Omega$, 1A to 4A



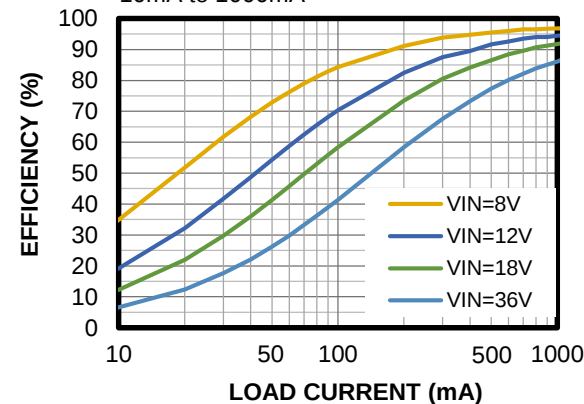
Efficiency vs. Load Current

FCCM, $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$,
0.1mA to 10mA



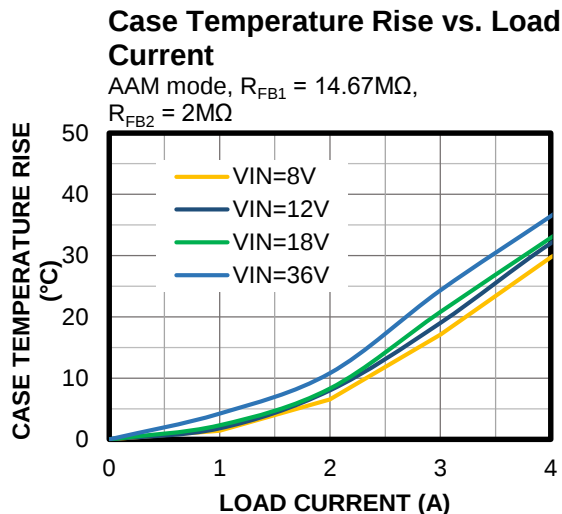
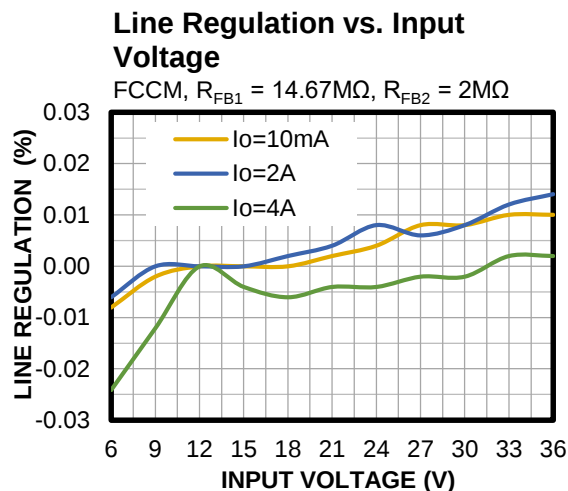
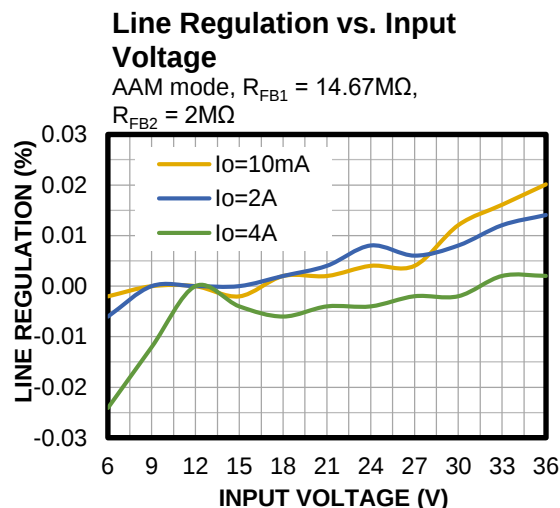
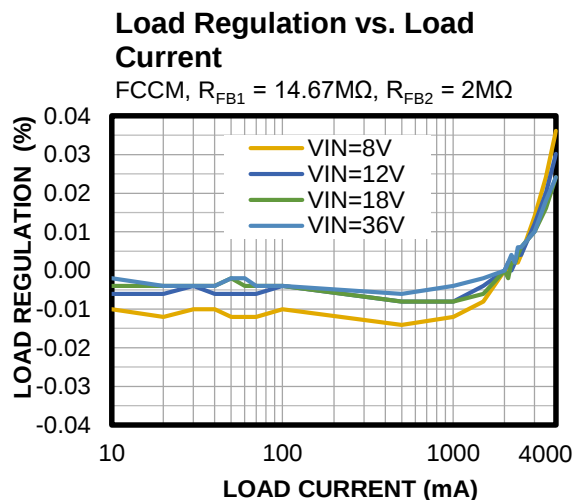
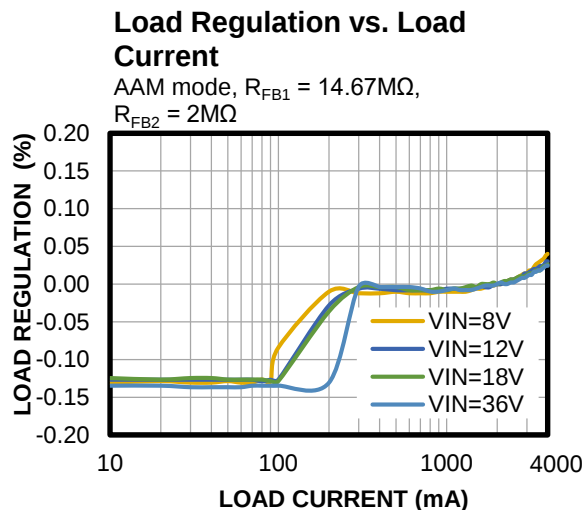
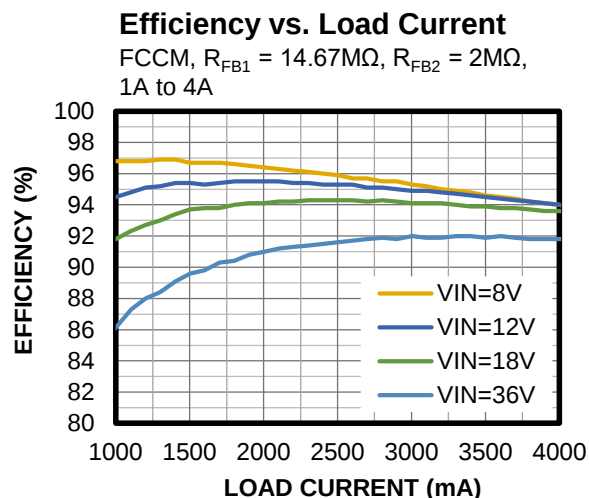
Efficiency vs. Load Current

FCCM, $R_{FB1} = 14.67M\Omega$, $R_{FB2} = 2M\Omega$,
10mA to 1000mA



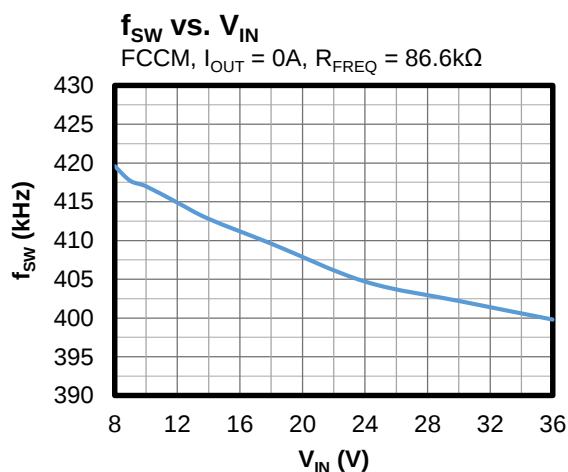
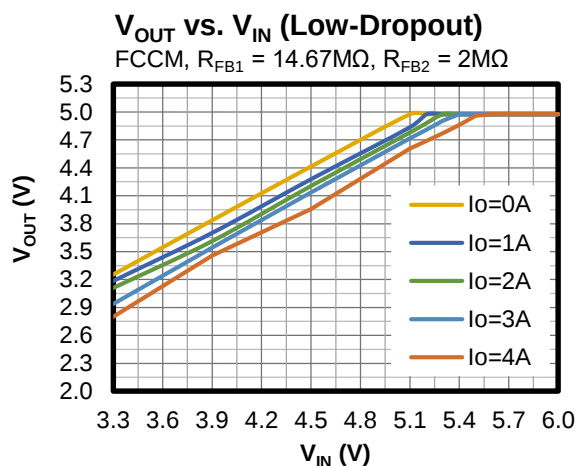
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 4.7\mu H$ (DCR = 14.4m Ω), $f_{SW} = 410kHz$, $T_A = 25^\circ C$, unless otherwise noted.



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 4.7\mu H$ (DCR = $14.4m\Omega$), $f_{SW} = 410kHz$, $T_A = 25^\circ C$, unless otherwise noted.

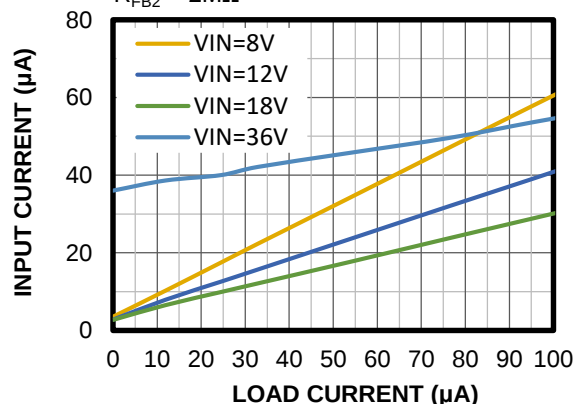


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.7V$, $L = 1\mu H$ (DCR = $9.4m\Omega$), $f_{SW} = 2.2MHz$, $T_A = 25^\circ C$, unless otherwise noted.

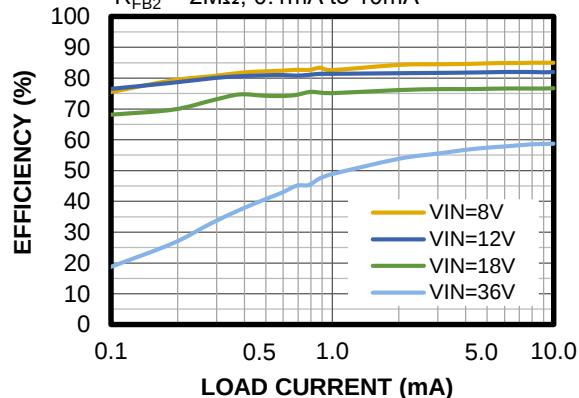
Input Current vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$



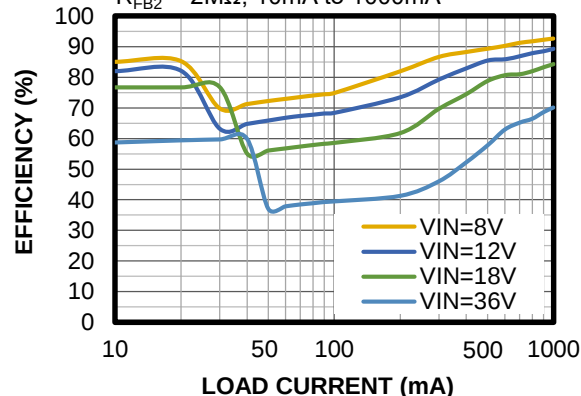
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$, 0.1mA to 10mA



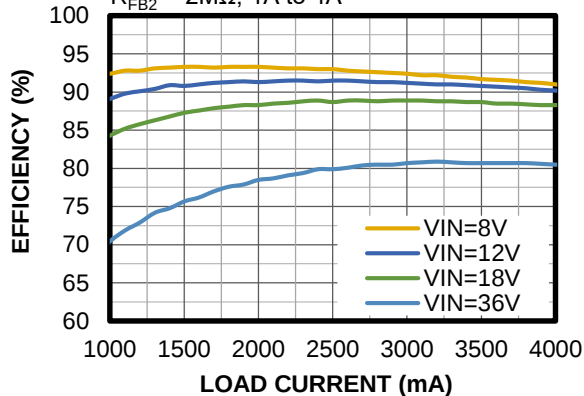
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$, 10mA to 1000mA



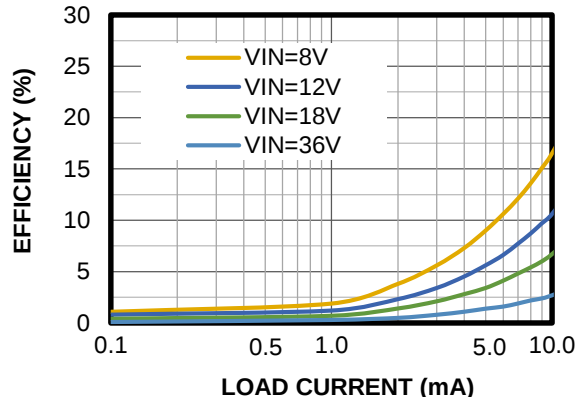
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$, 1A to 4A



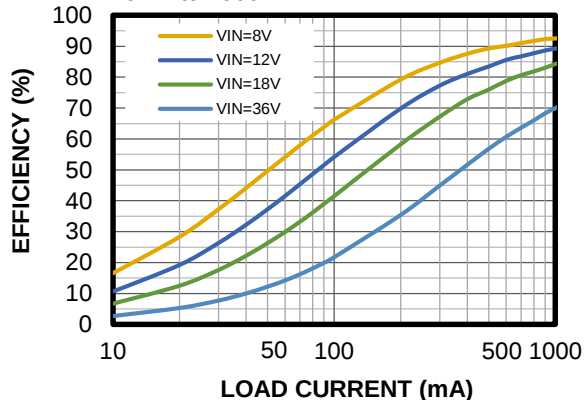
Efficiency vs. Load Current

FCCM, $R_{FB1} = 10.33M\Omega$, $R_{FB2} = 2M\Omega$,
0.1mA to 10mA



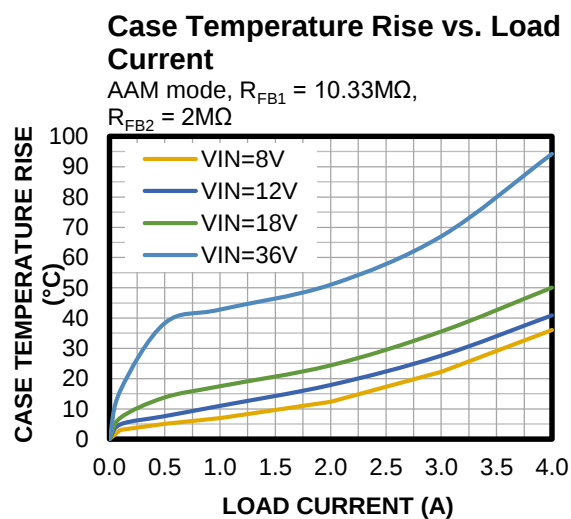
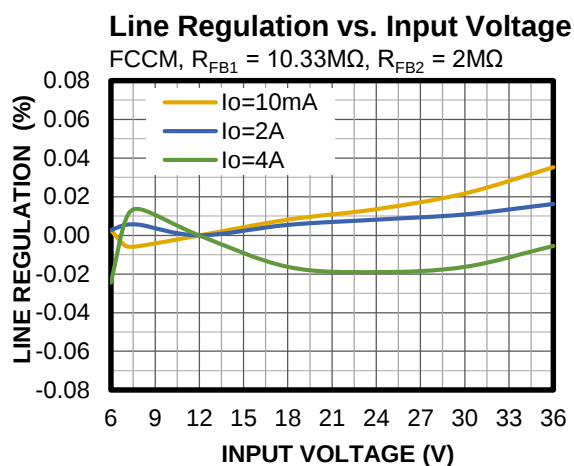
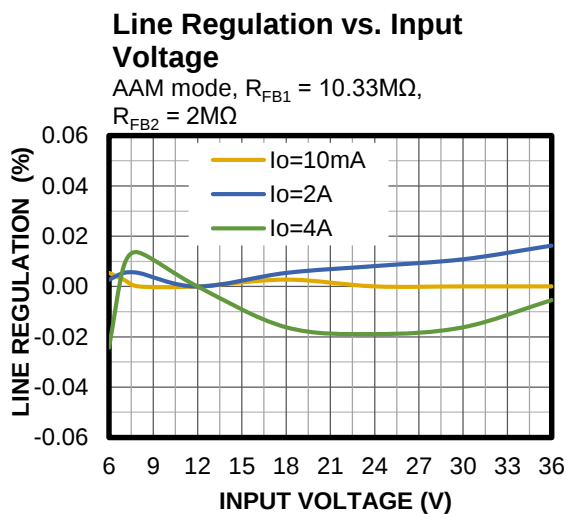
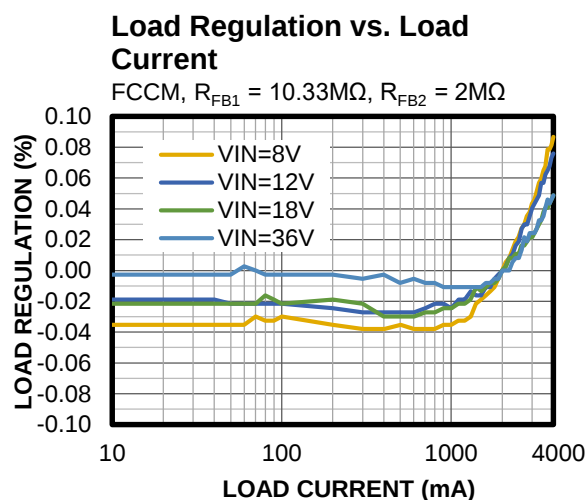
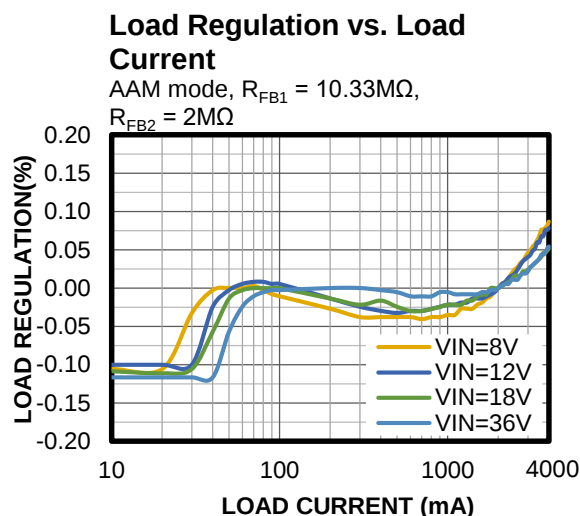
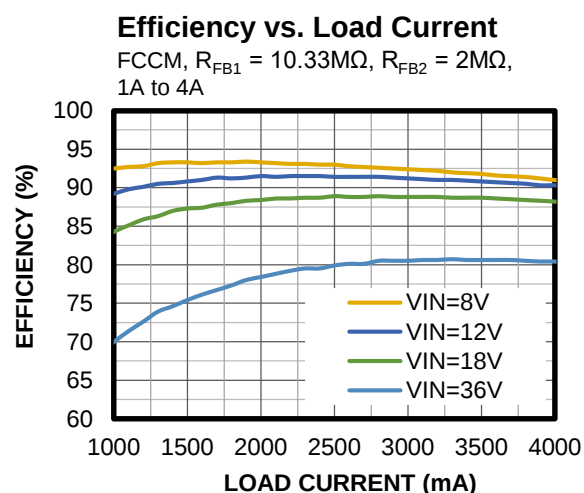
Efficiency vs. Load Current

FCCM, $R_{FB1} = 10.33M\Omega$, $R_{FB2} = 2M\Omega$,
10mA to 1000mA



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.7V$, $L = 1\mu H$ (DCR = $9.4m\Omega$), $f_{SW} = 2.2MHz$, $T_A = 25^\circ C$, unless otherwise noted.

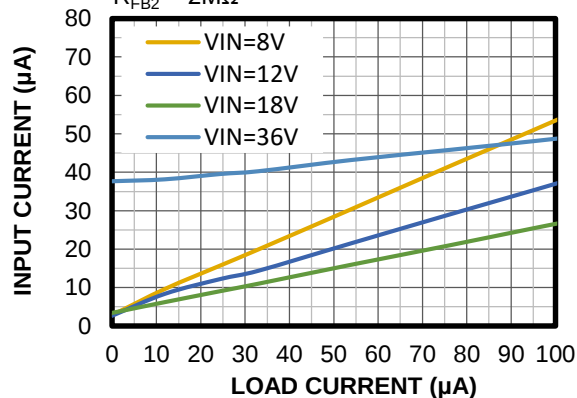


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.7V$, $L = 4.7\mu H$ (DCR = 14.4m Ω), $f_{SW} = 410kHz$, $T_A = 25^\circ C$, unless otherwise noted.

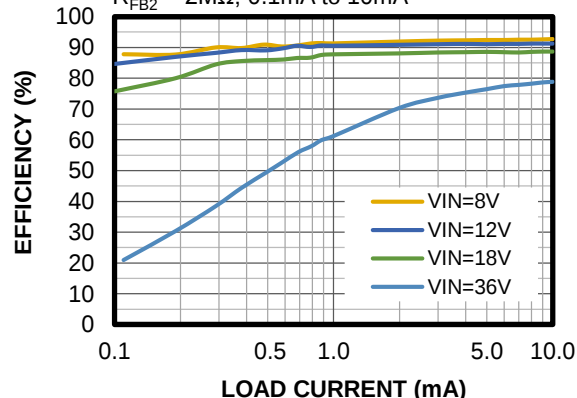
Input Current vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$



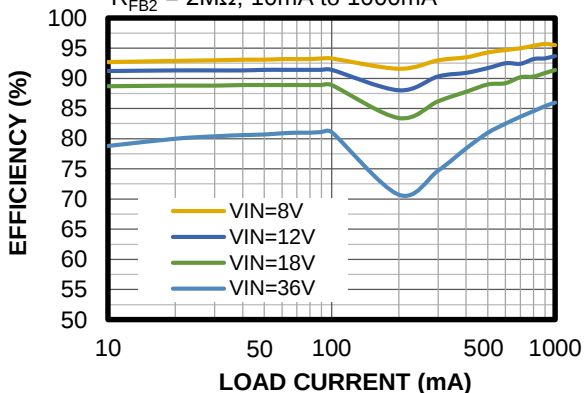
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$, 0.1mA to 10mA



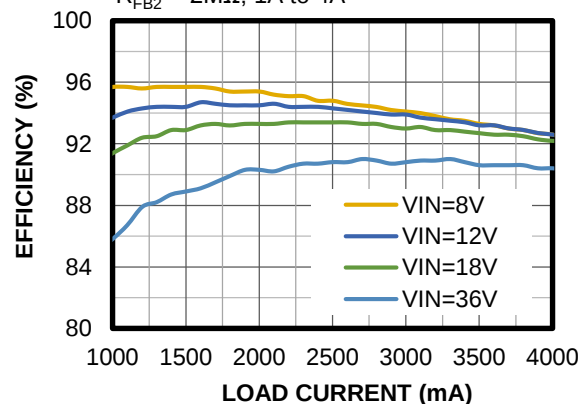
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$, 10mA to 1000mA



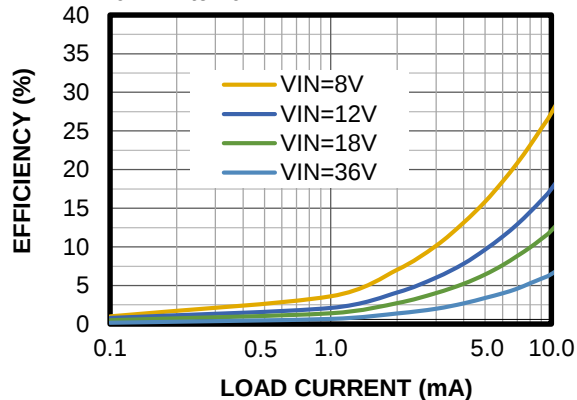
Efficiency vs. Load Current

AAM mode, $R_{FB1} = 10.33M\Omega$,
 $R_{FB2} = 2M\Omega$, 1A to 4A



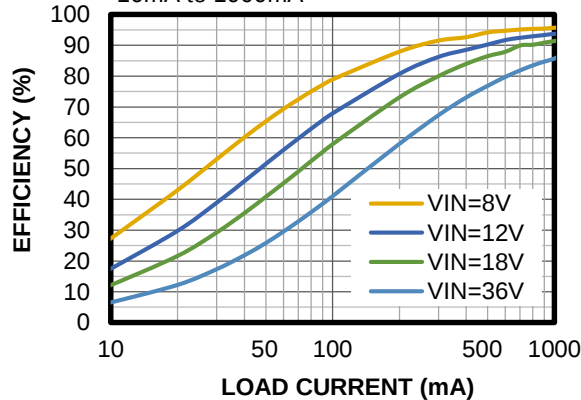
Efficiency vs. Load Current

FCCM, $R_{FB1} = 10.33M\Omega$, $R_{FB2} = 2M\Omega$,
0.1mA to 10mA



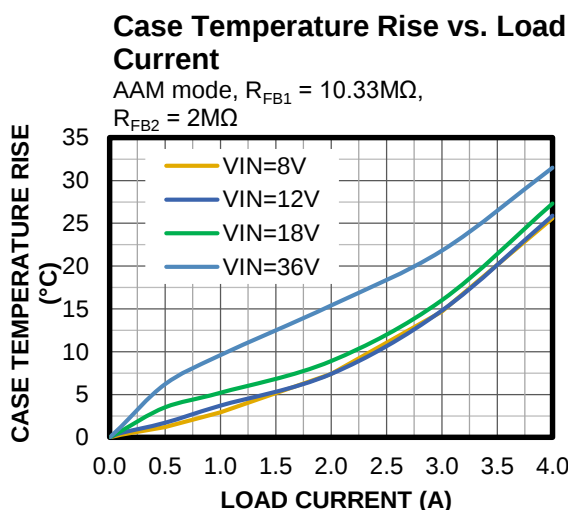
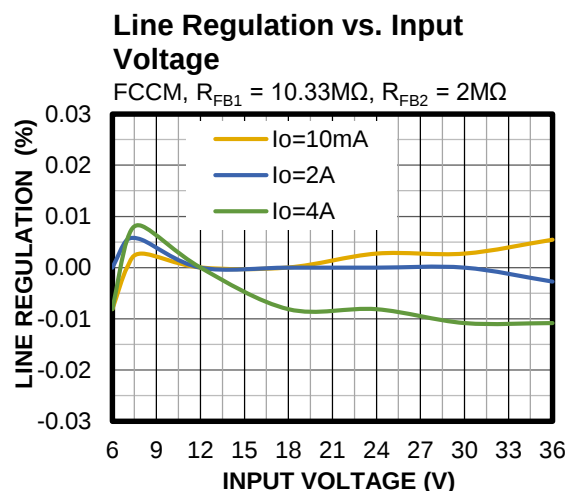
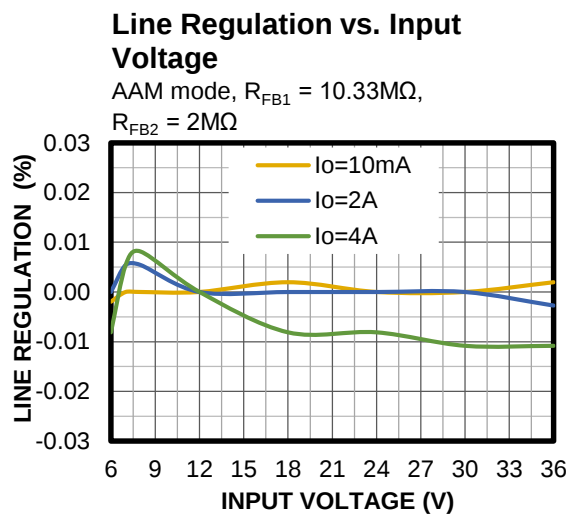
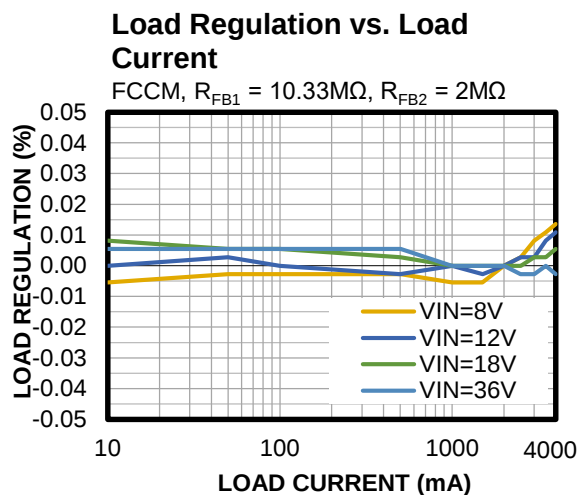
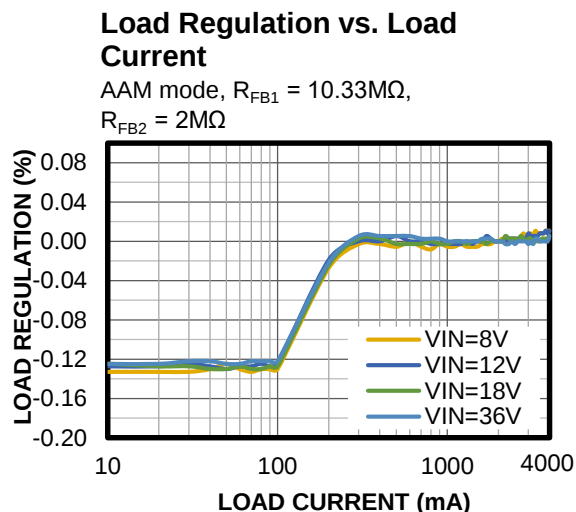
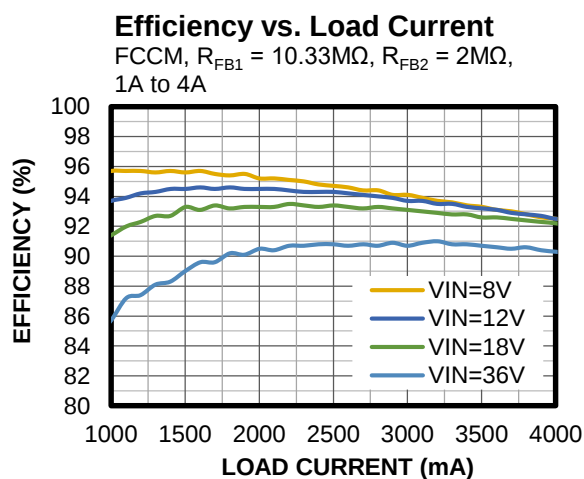
Efficiency vs. Load Current

FCCM, $R_{FB1} = 10.33M\Omega$, $R_{FB2} = 2M\Omega$,
10mA to 1000mA



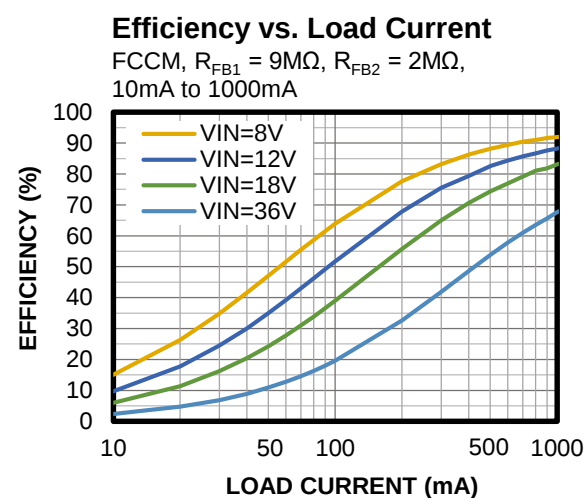
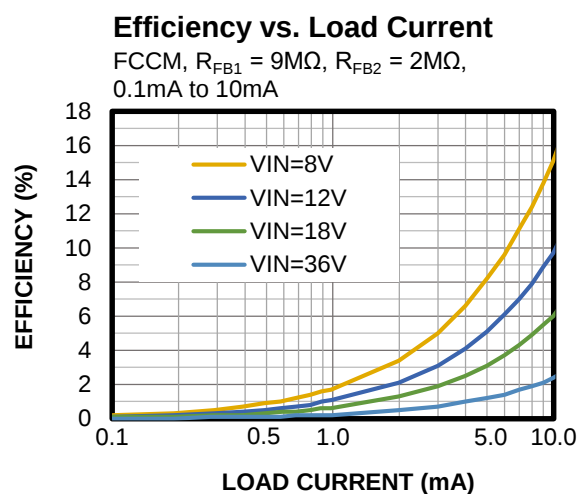
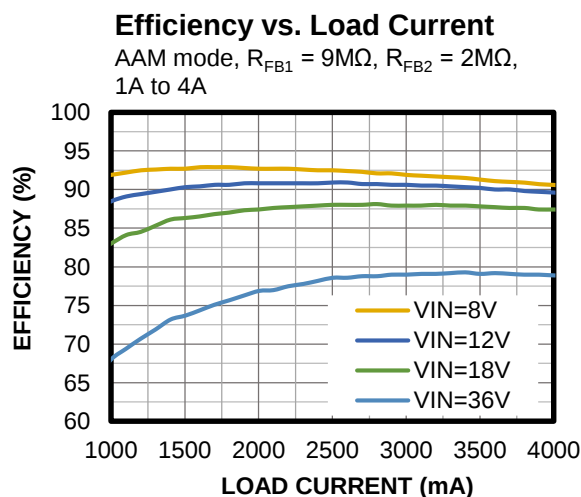
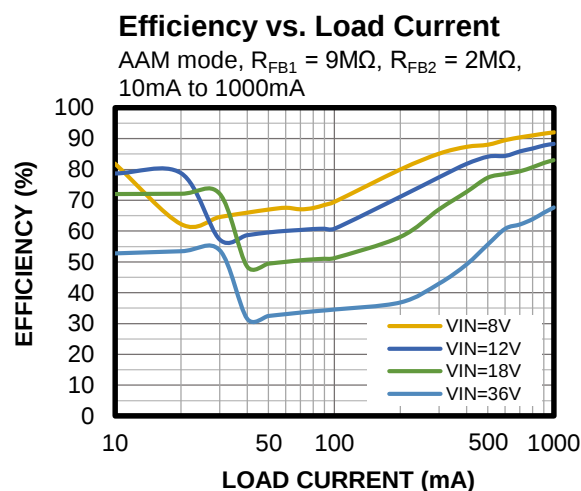
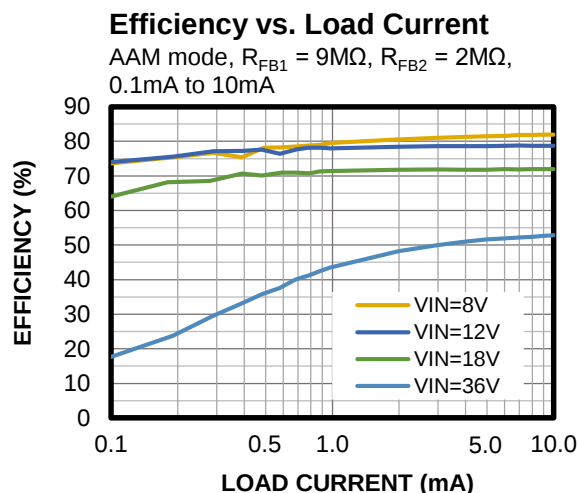
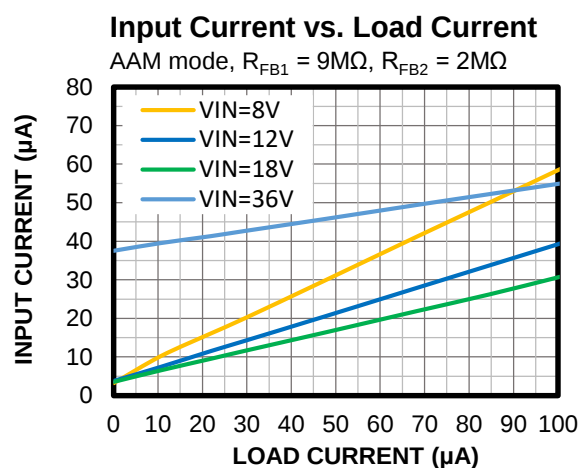
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.7V$, $L = 4.7\mu H$ (DCR = 14.4m Ω), $f_{SW} = 410kHz$, $T_A = 25^\circ C$, unless otherwise noted.



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.3V$, $L = 1\mu H$ (DCR = $9.4m\Omega$), $f_{SW} = 2.2MHz$, $T_A = 25^\circ C$, unless otherwise noted.

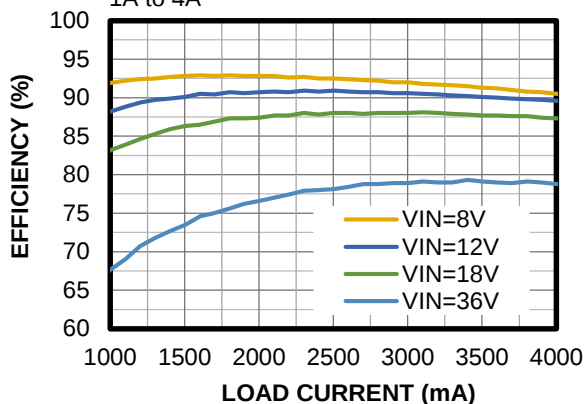


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.3V$, $L = 1\mu H$ (DCR = $9.4m\Omega$), $f_{SW} = 2.2MHz$, $T_A = 25^\circ C$, unless otherwise noted.

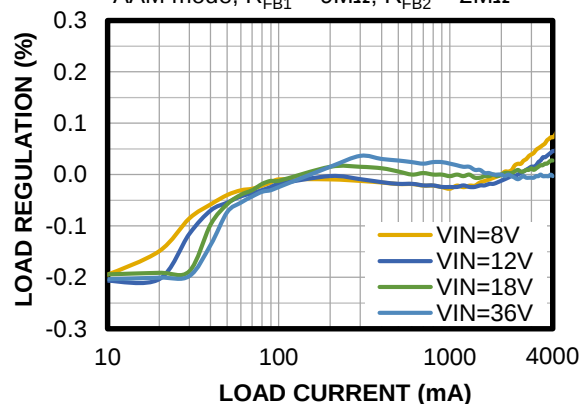
Efficiency vs. Load Current

FCCM, $R_{FB1} = 9M\Omega$, $R_{FB2} = 2M\Omega$,
1A to 4A



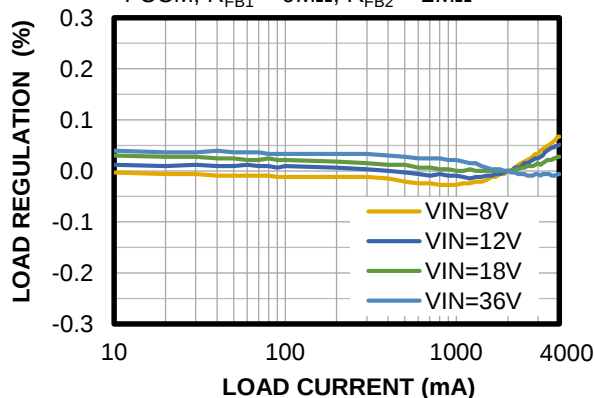
Load Regulation vs. Load Current

AAM mode, $R_{FB1} = 9M\Omega$, $R_{FB2} = 2M\Omega$



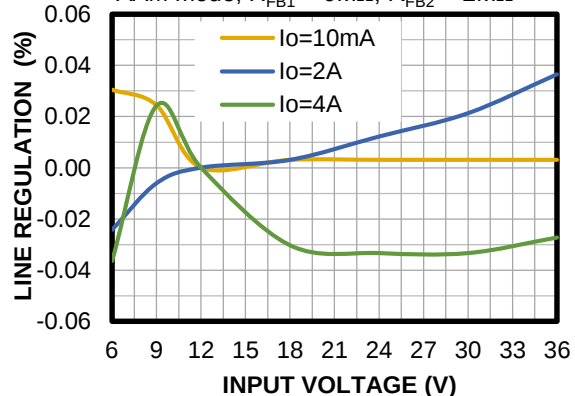
Load Regulation vs. Load Current

FCCM, $R_{FB1} = 9M\Omega$, $R_{FB2} = 2M\Omega$



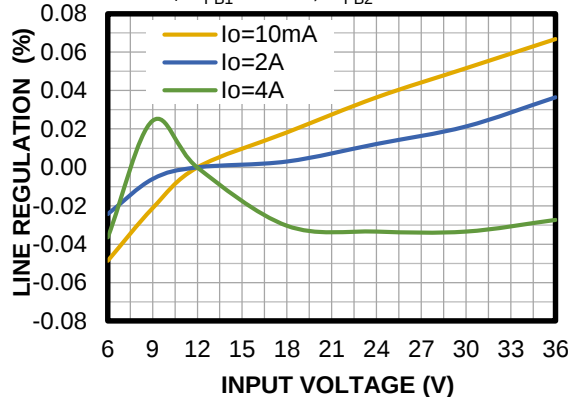
Line Regulation vs. Input Voltage

AAM mode, $R_{FB1} = 9M\Omega$, $R_{FB2} = 2M\Omega$



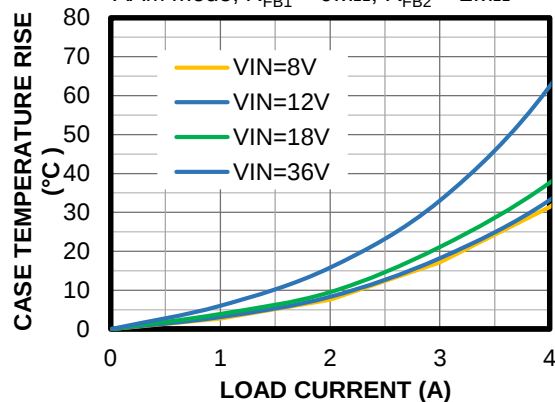
Line Regulation vs. Input Voltage

FCCM, $R_{FB1} = 9M\Omega$, $R_{FB2} = 2M\Omega$



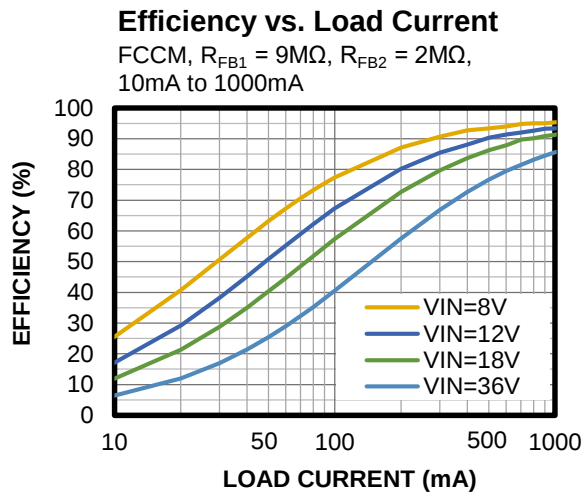
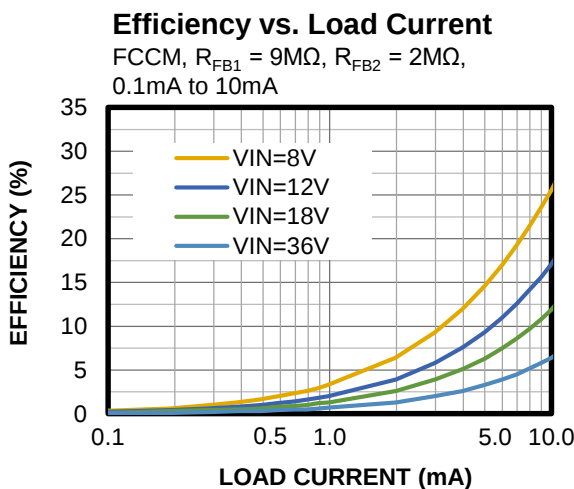
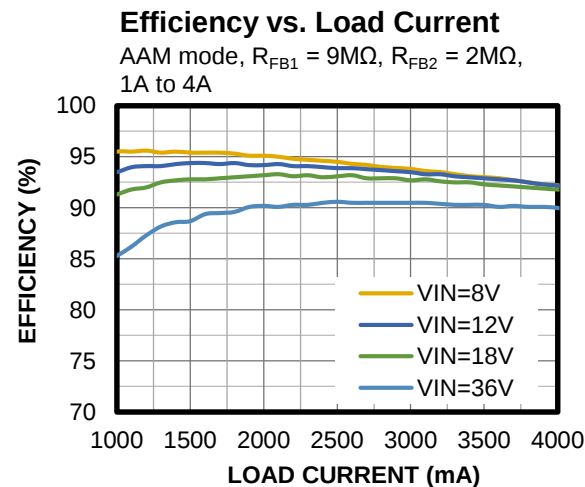
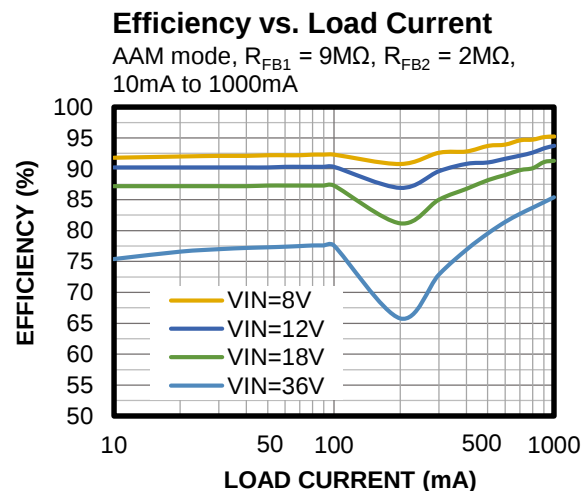
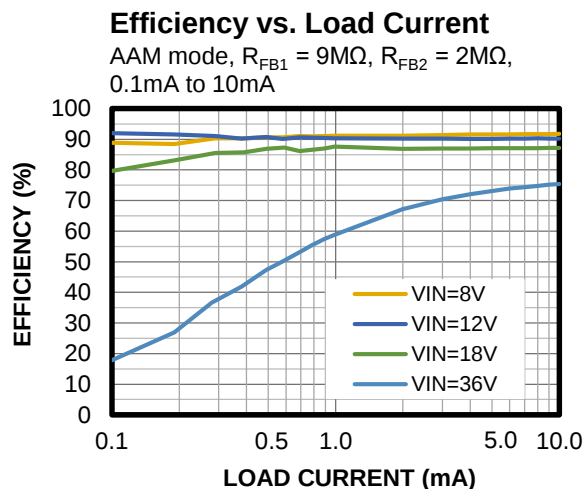
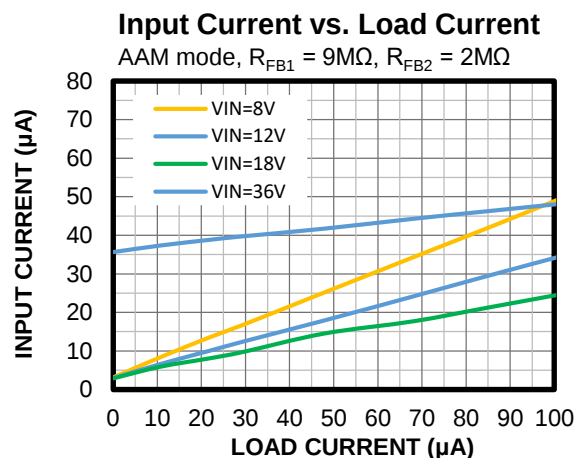
Case Temperature Rise vs. Load Current

AAM mode, $R_{FB1} = 9M\Omega$, $R_{FB2} = 2M\Omega$



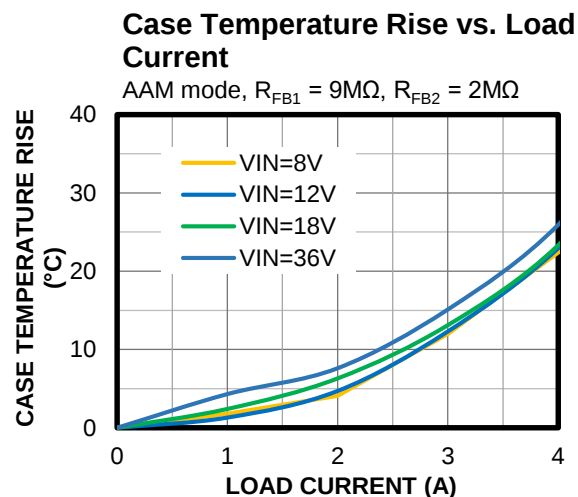
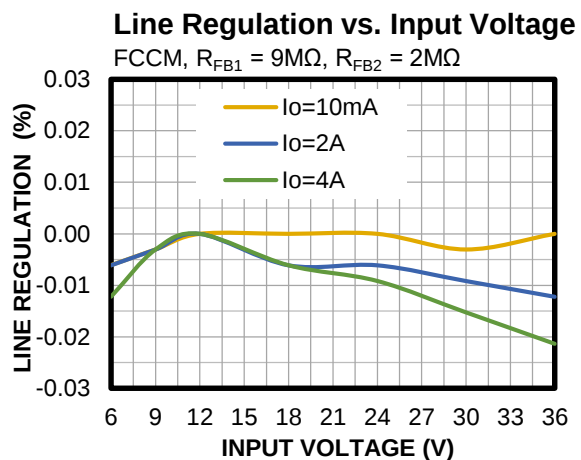
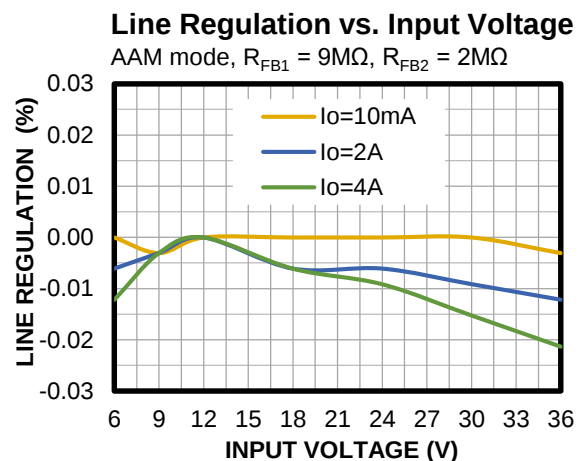
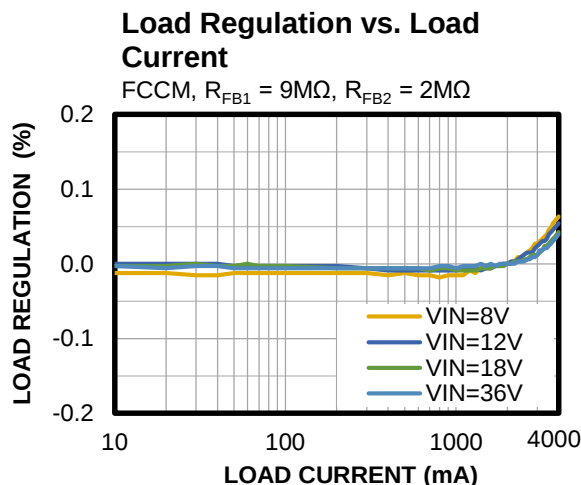
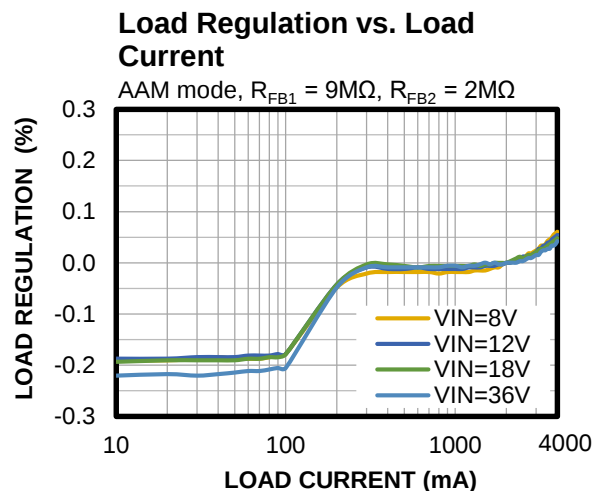
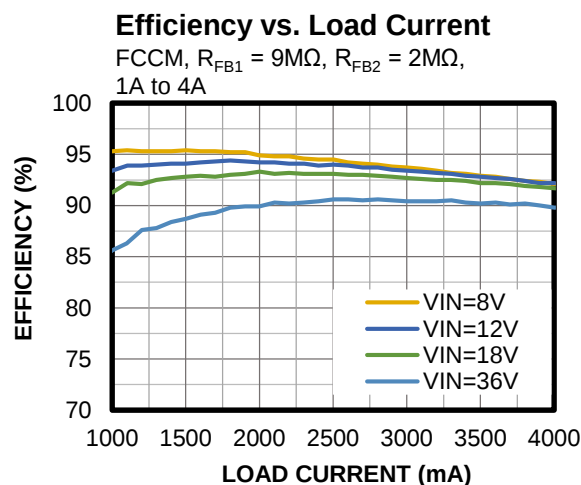
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.3V$, $L = 4.7\mu H$ (DCR = 14.4m Ω), $f_{SW} = 410kHz$, $T_A = 25^\circ C$, unless otherwise noted.



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 3.3V$, $L = 4.7\mu H$ (DCR = 14.4m Ω), $f_{SW} = 410kHz$, $T_A = 25^\circ C$, unless otherwise noted.

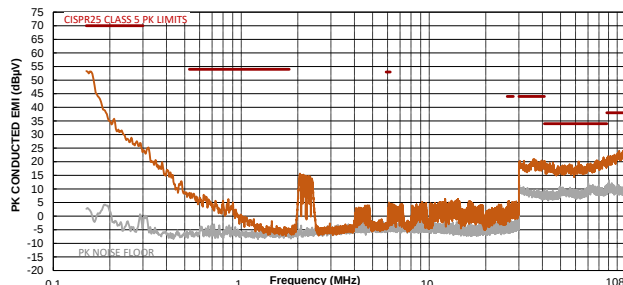


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$ ⁽¹⁰⁾, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted. ⁽¹¹⁾

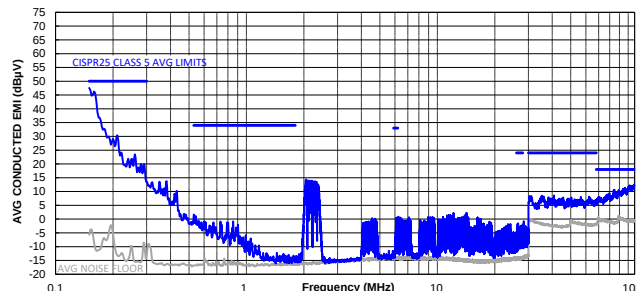
CISPR25 Class 5 Peak Conducted Emissions

150kHz to 108MHz



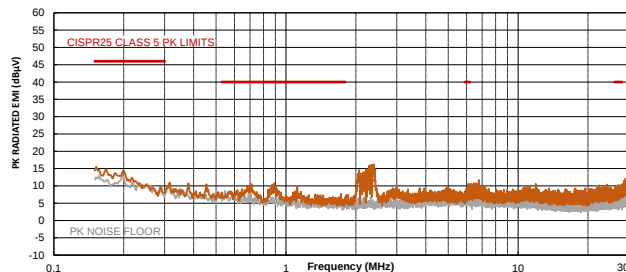
CISPR25 Class 5 Average Conducted Emissions

150kHz to 108MHz



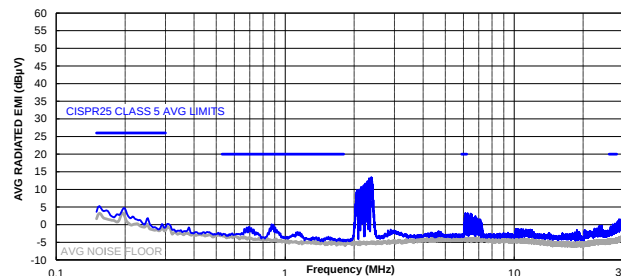
CISPR25 Class 5 Peak Radiated Emissions

150kHz to 30MHz



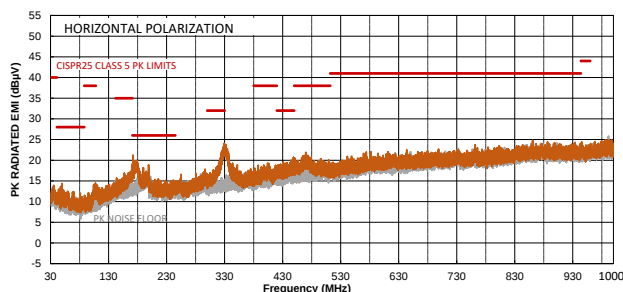
CISPR25 Class 5 Average Radiated Emissions

150kHz to 30MHz



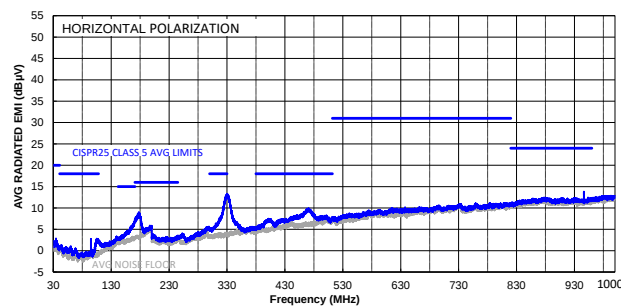
CISPR25 Class 5 Peak Radiated Emissions

Horizontal, 30MHz to 1GHz



CISPR25 Class 5 Average Radiated Emissions

Horizontal, 30MHz to 1GHz

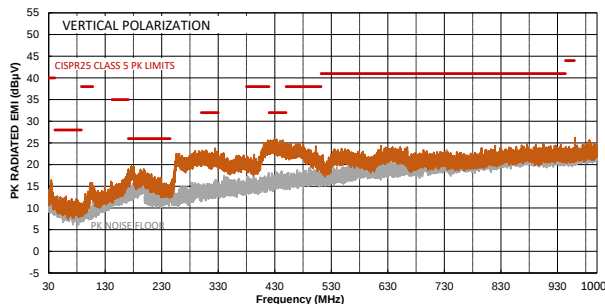


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$ ⁽¹⁰⁾, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted. ⁽¹¹⁾

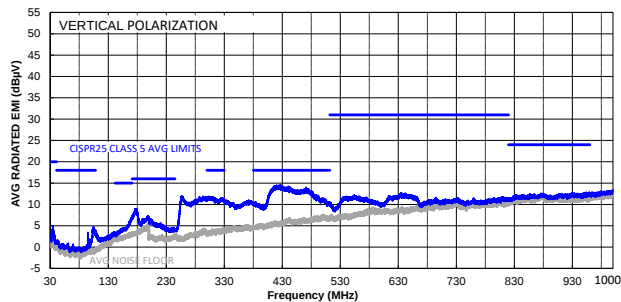
CISPR25 Class 5 Peak Radiated Emissions

Vertical, 30MHz to 1GHz



CISPR25 Class 5 Average Radiated Emissions

Vertical, 30MHz to 1GHz



Notes:

10) Inductor part number: XAL5030-102MEB/C. DCR = 9.4mΩ.

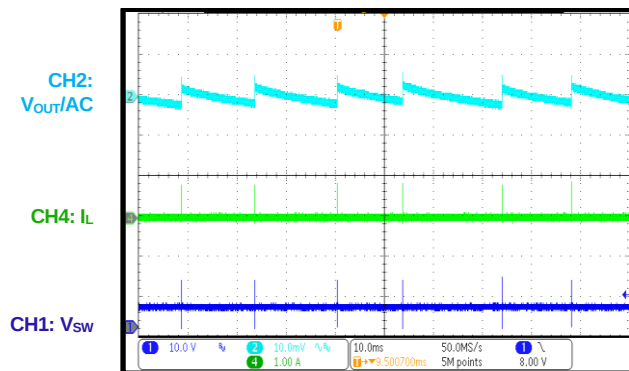
11) The EMC test results are based on the application circuit with EMI filters (see Figure 15 on page 49).

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted.

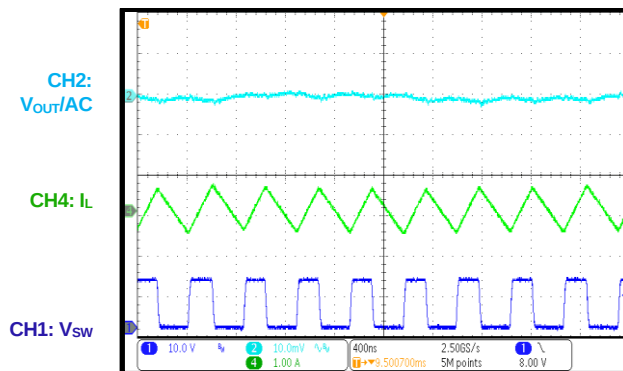
Steady State

$I_{OUT} = 0A$, AAM mode



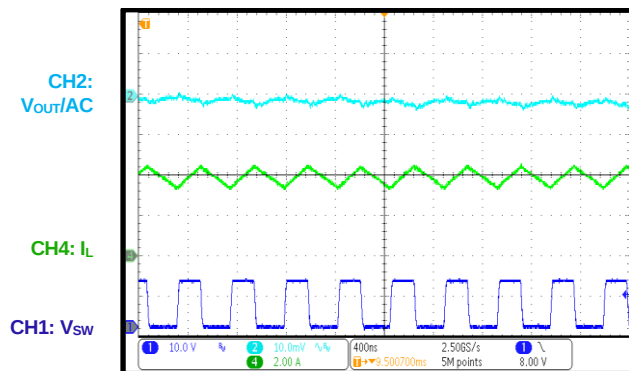
Steady State

$I_{OUT} = 0A$, FCCM



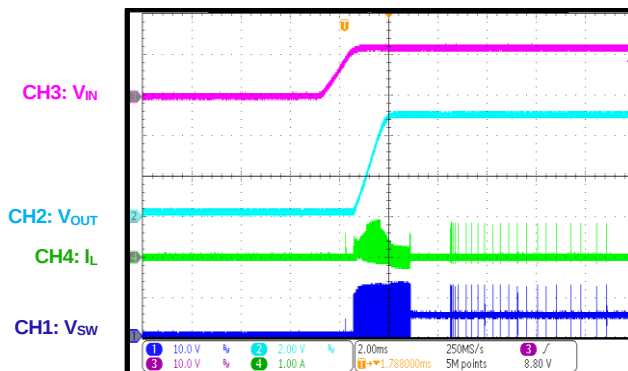
Steady State

$I_{OUT} = 4A$



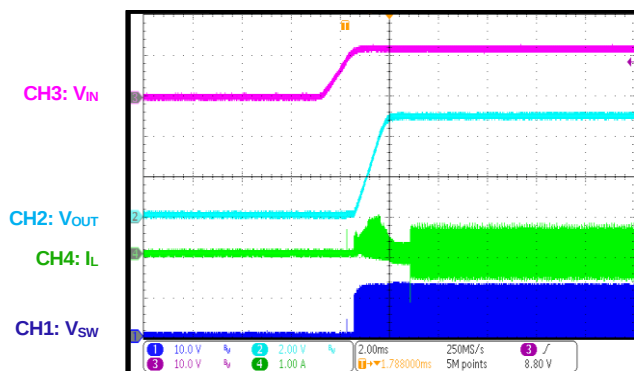
Start-Up through VIN

$I_{OUT} = 0A$, AAM mode



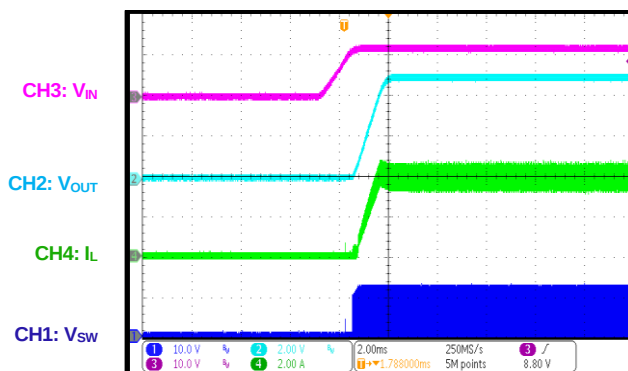
Start-Up through VIN

$I_{OUT} = 0A$, FCCM



Start-Up through VIN

$I_{OUT} = 4A$

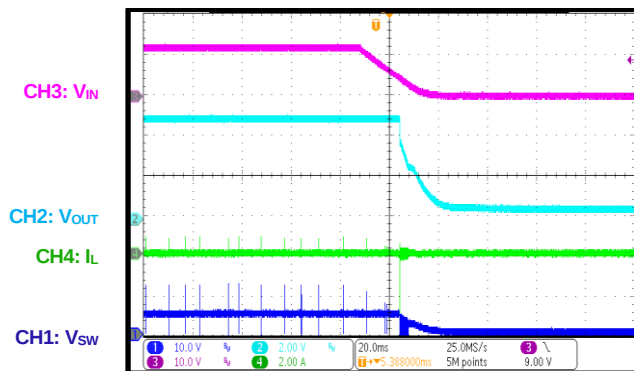


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted.

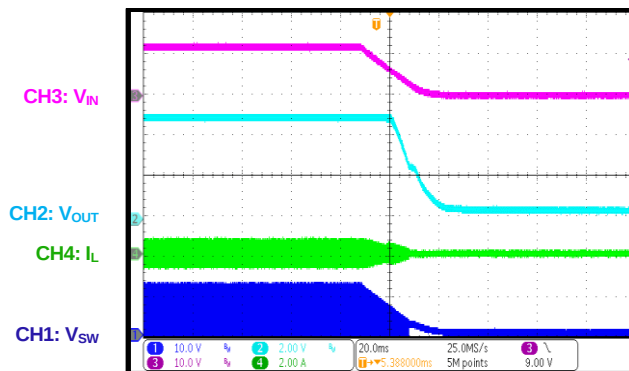
Shutdown through VIN

$I_{OUT} = 0A$, AAM mode



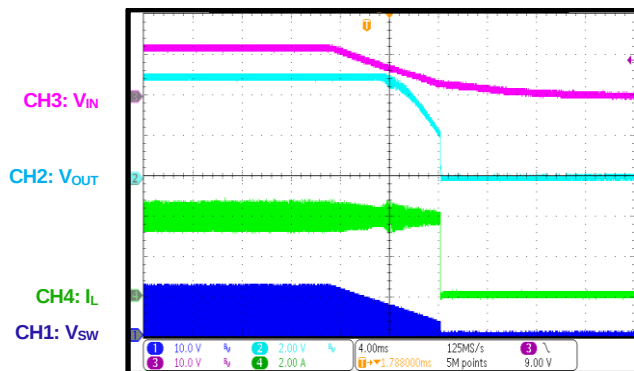
Shutdown through VIN

$I_{OUT} = 0A$, FCCM



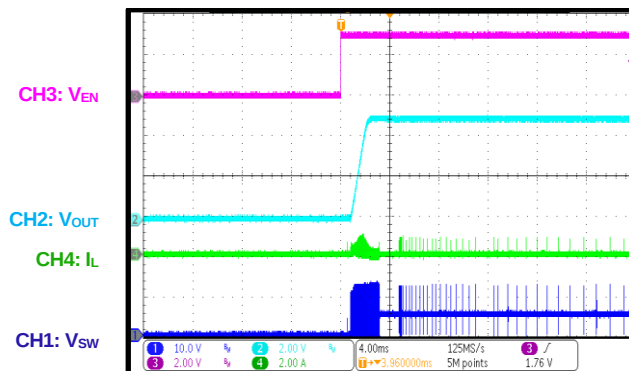
Shutdown through VIN

$I_{OUT} = 4A$



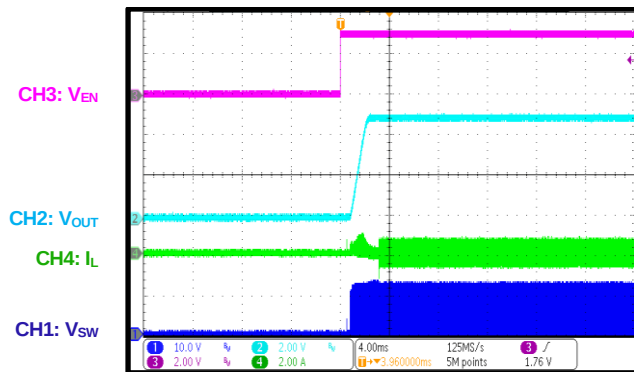
Start-Up through EN

$I_{OUT} = 0A$, AAM mode



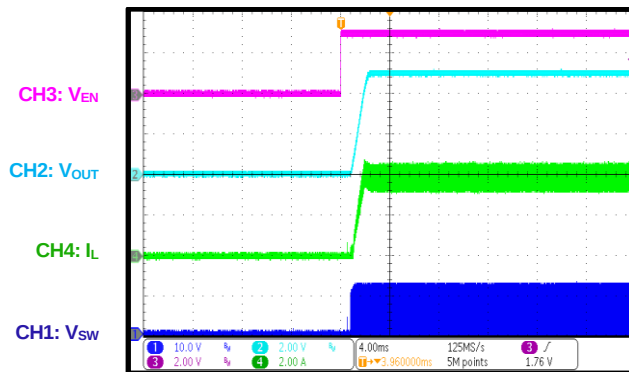
Start-Up through EN

$I_{OUT} = 0A$, FCCM



Start-Up through EN

$I_{OUT} = 4A$

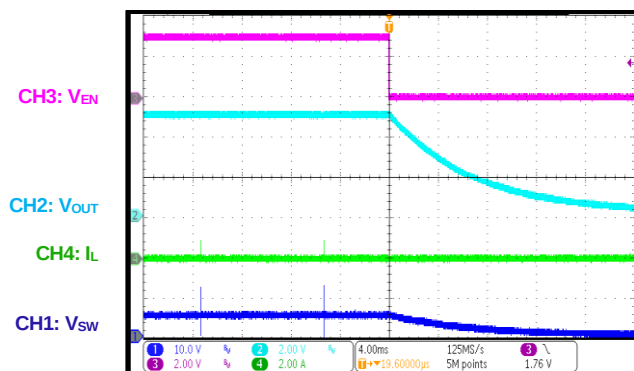


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted.

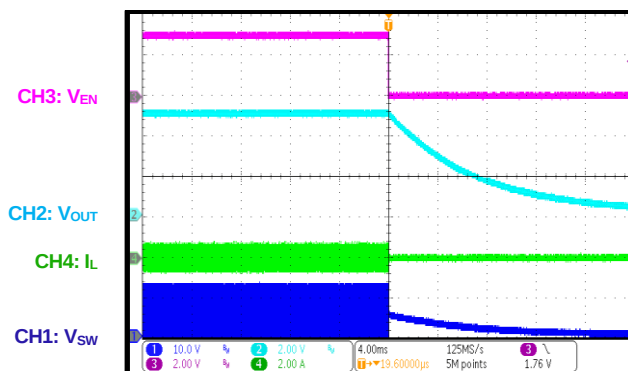
Shutdown through EN

$I_{OUT} = 0A$, AAM mode



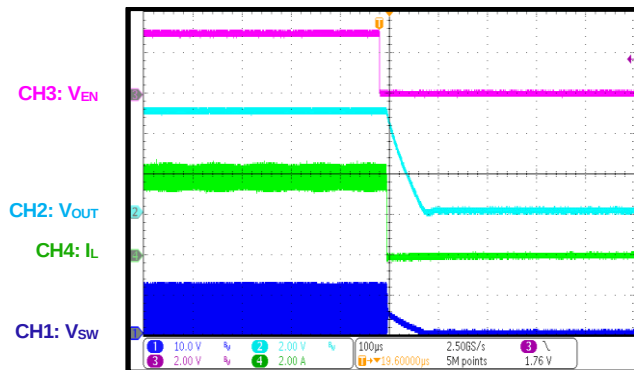
Shutdown through EN

$I_{OUT} = 0A$, FCCM



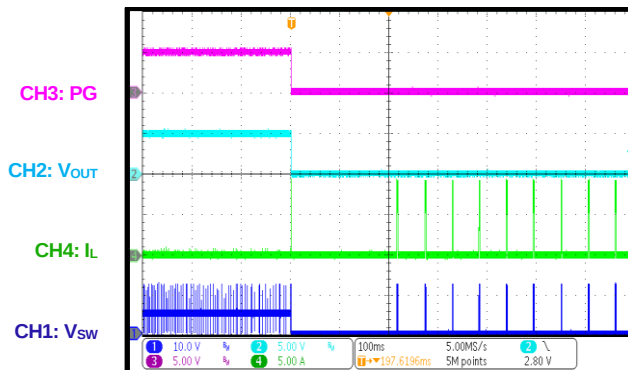
Shutdown through EN

$I_{OUT} = 4A$



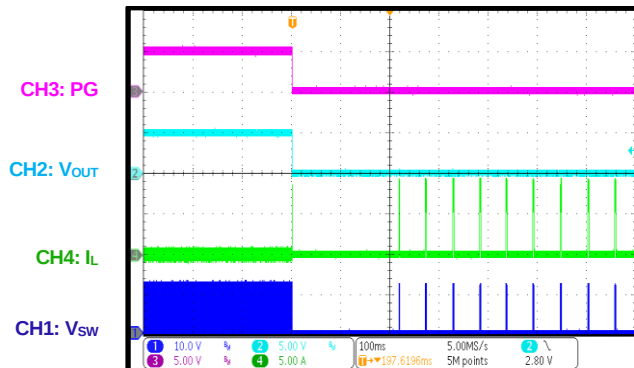
SCP Entry

$I_{OUT} = 0A$, AAM mode



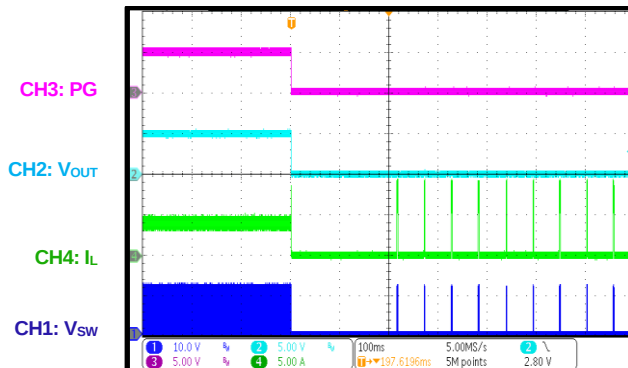
SCP Entry

$I_{OUT} = 0A$, FCCM



SCP Entry

$I_{OUT} = 4A$

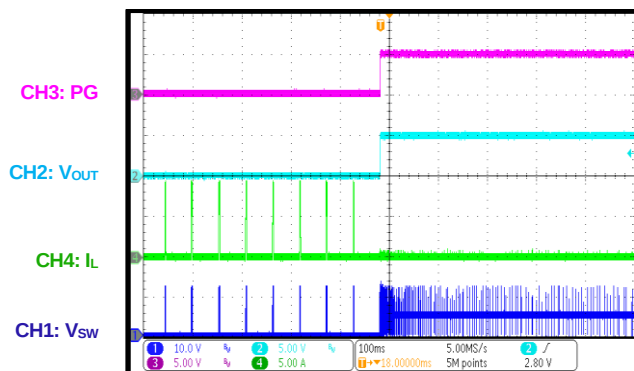


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted.

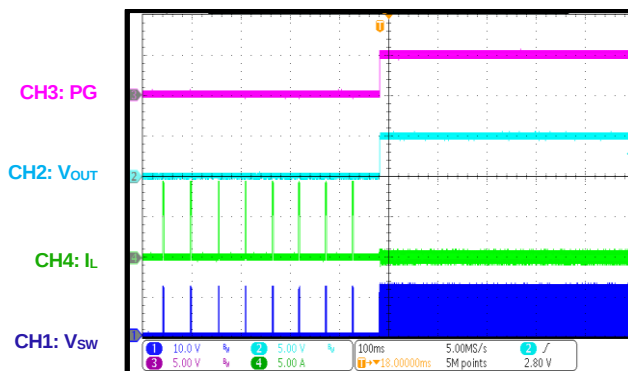
SCP Recovery

$I_{OUT} = 0A$, AAM mode



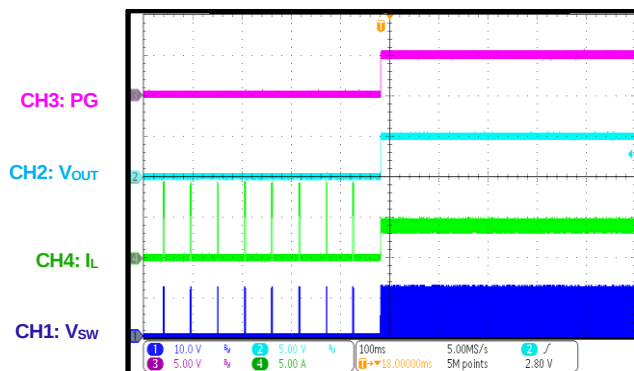
SCP Recovery

$I_{OUT} = 0A$, FCCM

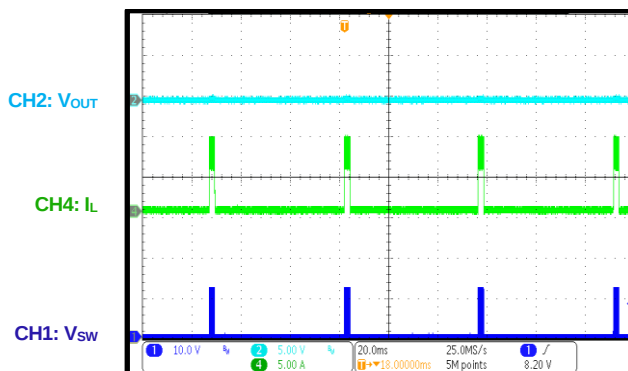


SCP Recovery

$I_{OUT} = 4A$

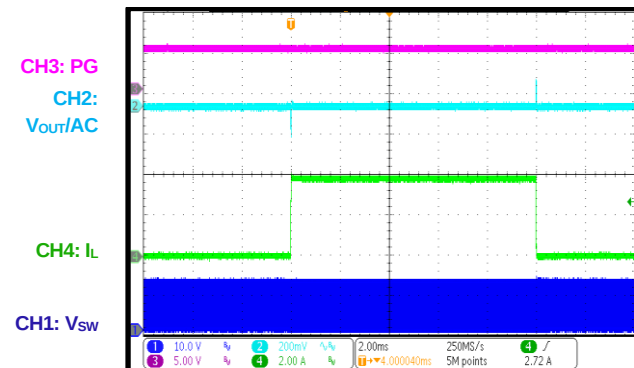


SCP Steady State



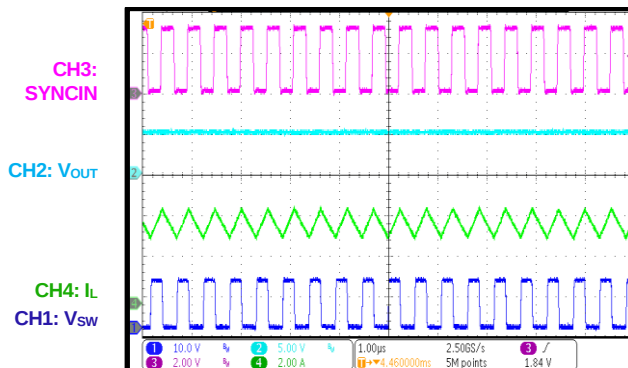
Load Transient Response

$I_{OUT} = 0A$ to $4A$, $1.6A/\mu s$



SYNCIN Operation

$I_{OUT} = 4A$, $f_{SW} = 2.2MHz$,
SYNCIN frequency = $1.9MHz$

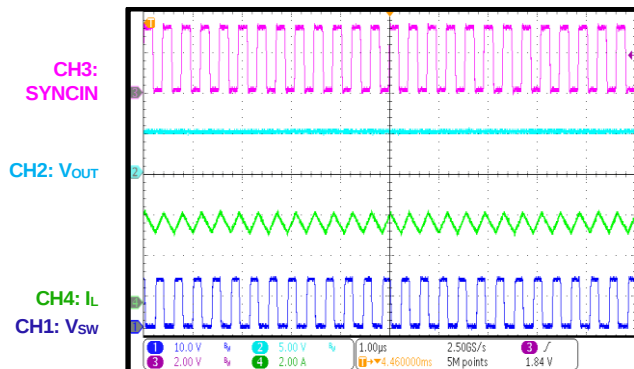


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted.

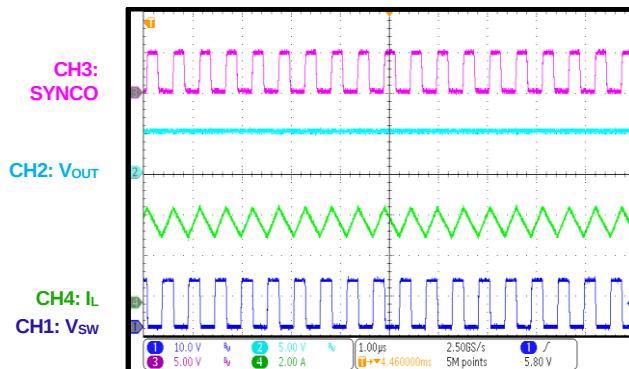
SYNCIN Operation

$I_{OUT} = 4A$, $f_{SW} = 2.2MHz$,
SYNCIN frequency = 2.6MHz



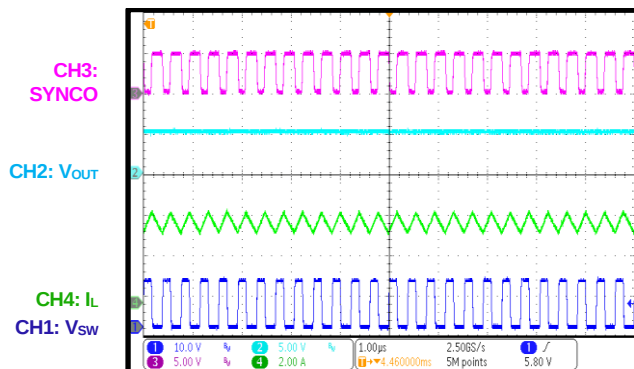
SYNCO Operation

$I_{OUT} = 4A$, $f_{SW} = 2.2MHz$,
SYNCIN frequency = 1.9MHz



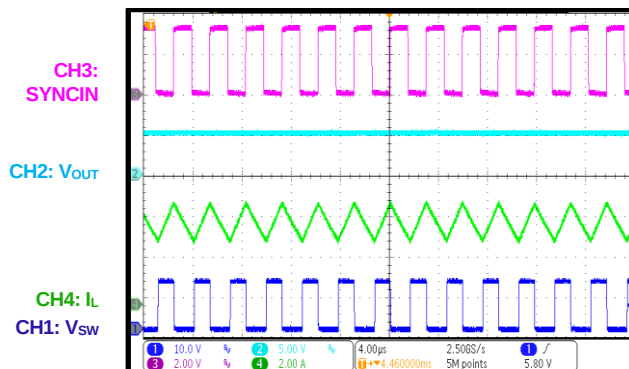
SYNCO Operation

$I_{OUT} = 4A$, $f_{SW} = 2.2MHz$,
SYNCIN frequency = 2.6MHz



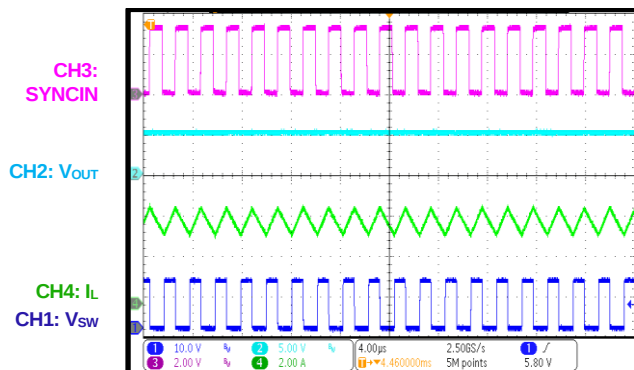
SYNCIN Operation

$I_{OUT} = 4A$, $f_{SW} = 410kHz$, $L = 4.7\mu H$,
SYNCIN frequency = 350kHz



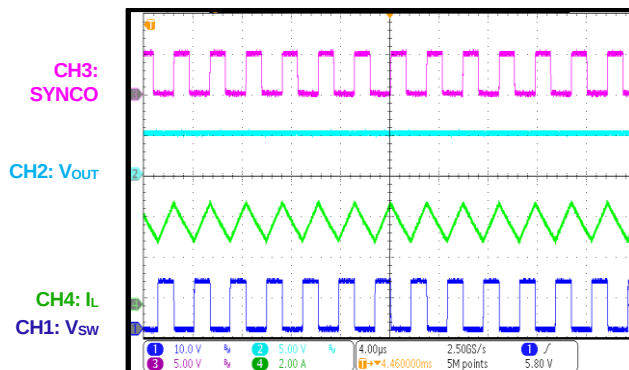
SYNCIN Operation

$I_{OUT} = 4A$, $f_{SW} = 410kHz$, $L = 4.7\mu H$,
SYNCIN frequency = 480kHz



SYNCO Operation

$I_{OUT} = 4A$, $f_{SW} = 410kHz$, $L = 4.7\mu H$,
SYNCIN frequency = 350kHz

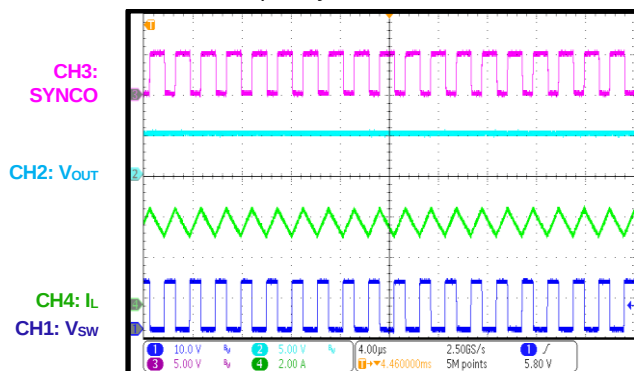


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted.

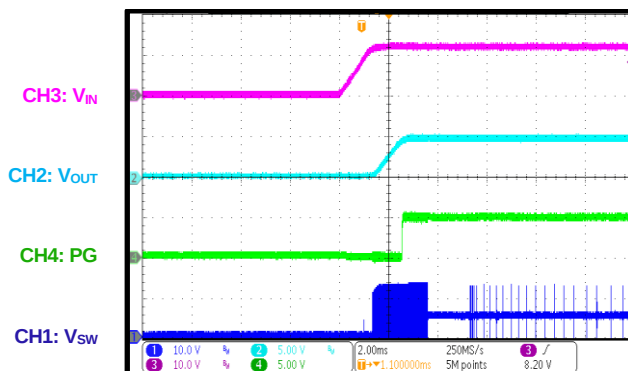
SYNCO Operation

$I_{OUT} = 4A$, $f_{sw} = 410kHz$, $L = 4.7\mu H$,
SYNCCIN frequency = 480kHz



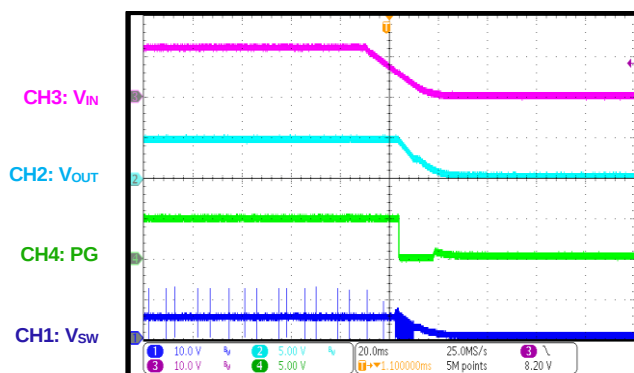
PG during Start-Up through V_{IN}

$I_{OUT} = 0A$, AAM mode



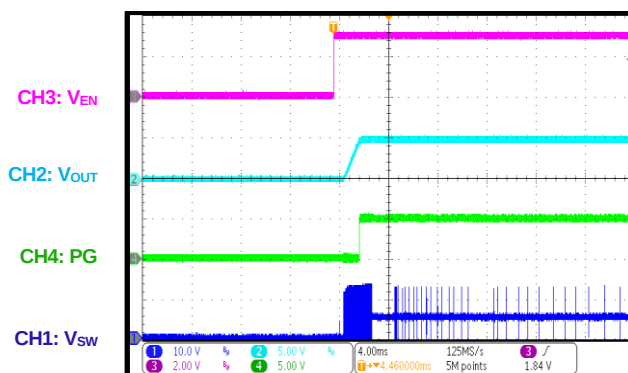
PG during Shutdown through V_{IN}

$I_{OUT} = 0A$, AAM mode



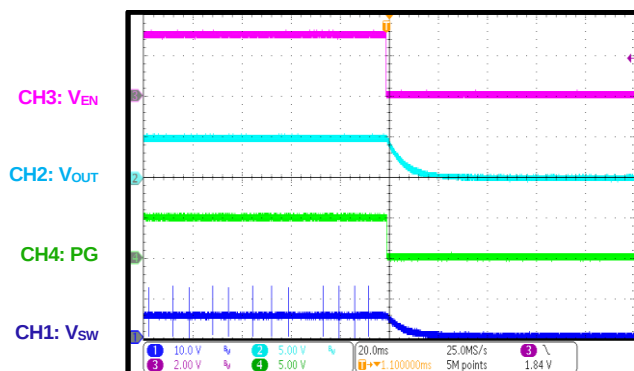
PG during Start-Up through EN

$I_{OUT} = 0A$, AAM mode



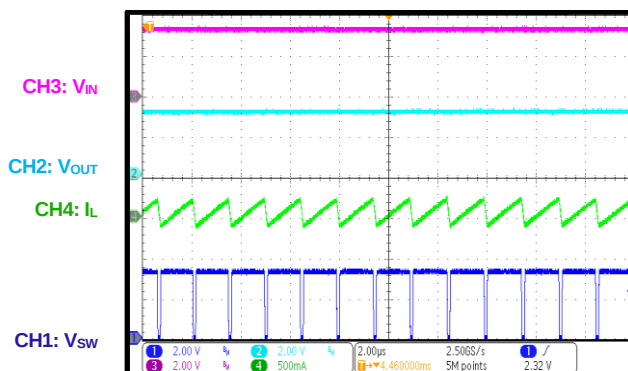
PG during Shutdown through EN

$I_{OUT} = 0A$, AAM mode



Dropout Operation

$V_{IN} = 3.3V$, $V_{OUT} = 5V$, $I_{OUT} = 0A$

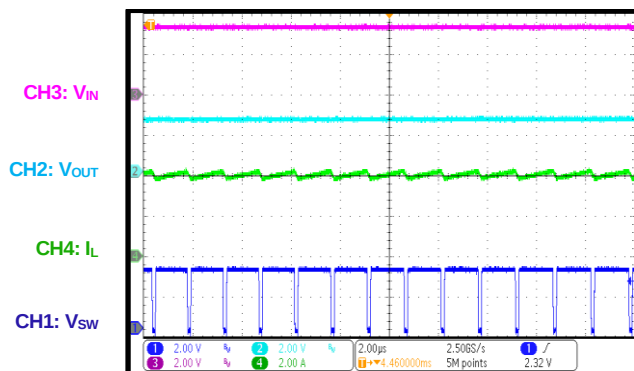


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{IN} = 12V$, $V_{OUT} = 5V$, $L = 1\mu H$, $f_{SW} = 2.2MHz$, AAM mode, $T_A = 25^\circ C$, unless otherwise noted.

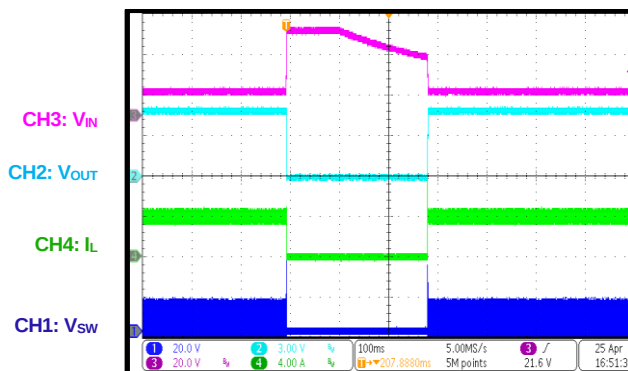
Low-Dropout Mode

$V_{IN} = 3.3V$, $V_{OUT} = 5V$, $I_{OUT} = 4A$



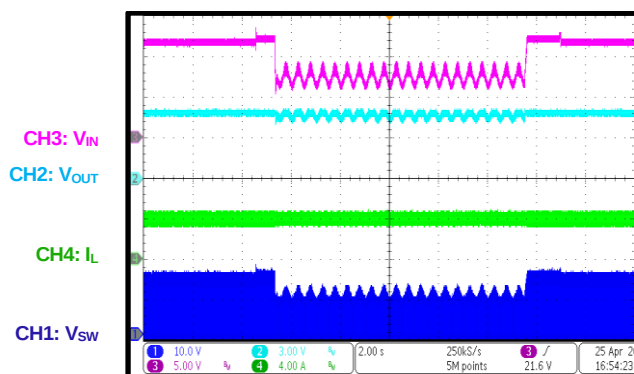
Load Dump

$V_{IN} = 12V$ to $42V$, $I_{OUT} = 4A$



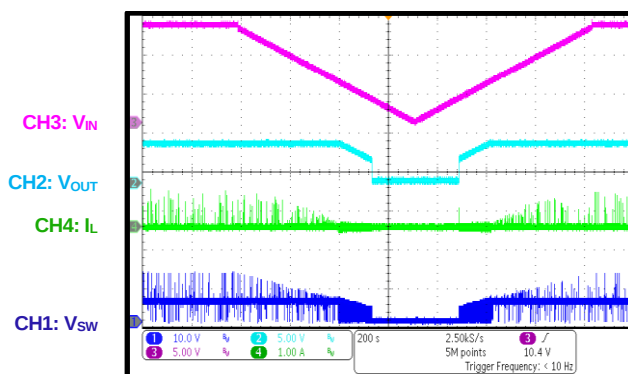
Cold Crank

$I_{OUT} = 4A$



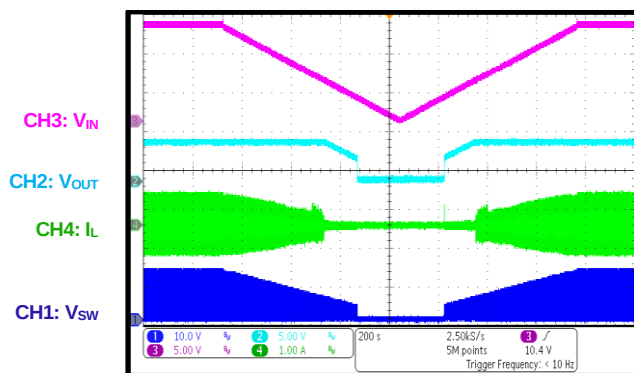
V_{IN} Ramping Up and Down

$I_{OUT} = 0A$, AAM mode



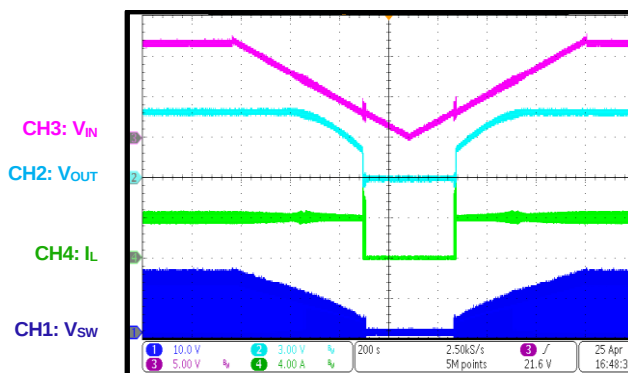
V_{IN} Ramping Up and Down

$I_{OUT} = 0A$, FCCM



V_{IN} Ramping Up and Down

$I_{OUT} = 4A$



FUNCTIONAL BLOCK DIAGRAM

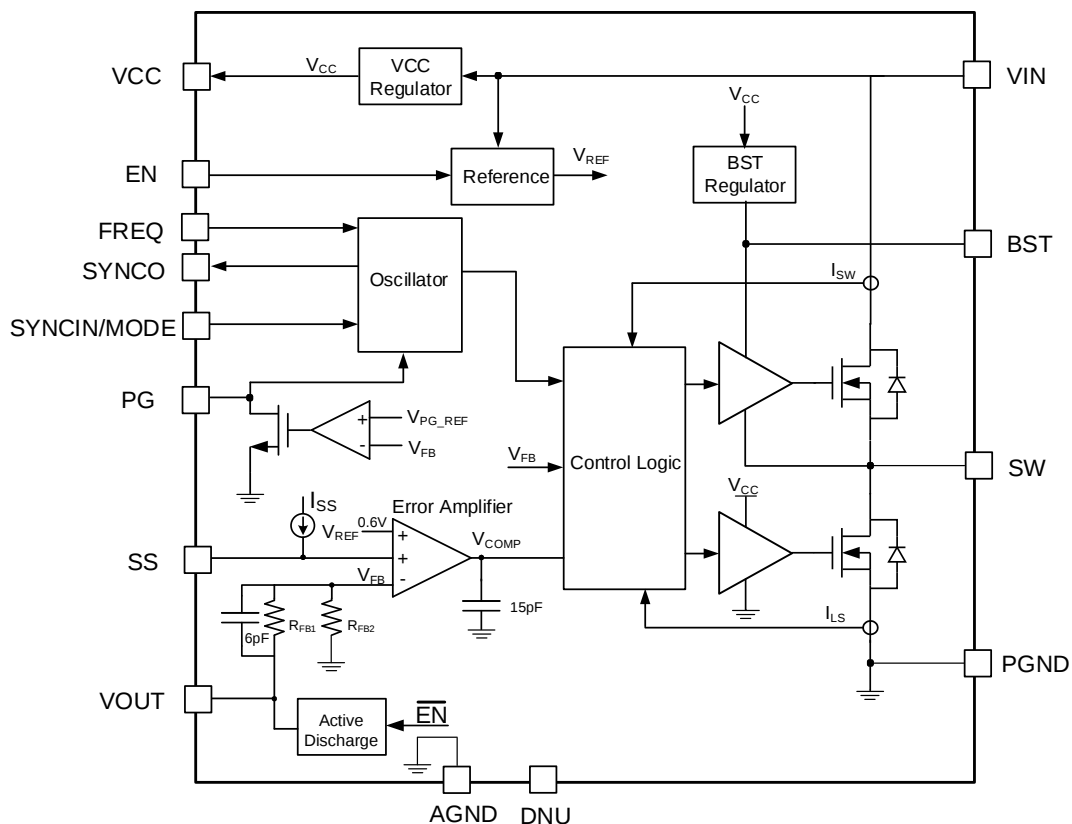


Figure 1: Functional Block Diagram

OPERATION

The MPQ4347/4347J is a synchronous, step-down switching regulator with integrated internal high-side and low-side MOSFETs (HS-FETs and LS-FETs, respectively). It provides 4A of highly efficient output current (I_{OUT}) with fixed frequency, zero-delay pulse-width module (PWM) control.

The device features a wide input voltage (V_{IN}) range, configurable 350kHz to 2.5MHz switching frequency (f_{SW}), external soft start, and precision current limit. Its very low operational quiescent current (I_Q) makes the MPQ4347/4347J well-suited for battery-powered applications.

Zero-Delay Pulse-Width Modulation (PWM) Control

Automotive applications typically require fixed-frequency operation to reduce EMI, but traditional fixed-frequency control topologies have major limitations. Voltage mode is difficult to compensate for in automotive environments, while peak current mode control cannot always keep up with stringent, modern system-on-chip (SoC) transient requirements without excessive output capacitance. With these requirements in mind, the MPQ4347/4347J introduces fixed frequency, zero-delay PWM control.

Zero-delay PWM control combines current information with hysteretic-style output voltage (V_{OUT}) control in a clocked system. This provides an optimal transient response, while maintaining a high phase margin across a wide variety of operating conditions and external component values. In addition, zero-delay PWM control provides superior EMI performance. The improved transient response reduces output capacitor requirements and lowers the system cost. Trailing-edge modulation facilitates a narrow minimum on time for high conversion ratio applications.

At the beginning of the PWM cycle, the HS-FET turns off and the LS-FET turns on immediately, then remains on until the control signal reaches the COMP voltage (V_{COMP}). The HS-FET remains off for at least 120ns at the beginning of the cycle.

Light-Load Operation

At moderate to high output currents, the MPQ4347/4347J operates at a fixed frequency. Under light-load conditions, the

MPQ4347/4347J can work in two different operation modes by setting the state of the SYNCIN/MODE pin.

When the SYNCIN/MODE pin is pulled above 1.8V or an external clock is used, the MPQ4347/4347J works in forced continuous conduction mode (FCCM). In FCCM, the device works with a fixed frequency from no-load to full-load conditions. The part has a reverse current limit (about -4A) to prevent the negative current from dropping too low and potentially damaging the components. Once the negative inductor current (I_L) reaches the reverse current limit, the LS-FET immediately turns off and the HS-FET turns on. The advantage of FCCM is its constant frequency and lower output ripple under light loads.

When the SYNCIN/MODE pin is pulled below 0.4V, the MPQ4347/4347J works in advanced asynchronous modulation (AAM) mode. The device cannot enter AAM mode until soft start (SS) finishes. AAM mode optimizes efficiency under light-load and no-load conditions.

In AAM mode, the LS-FET emulates a diode, and the HS-FET has a fixed one-shot on time to charge the inductor and regulate the output. As the load decreases, the interval between one-shots increases. When this interval exceeds 8 μ s, the part enters sleep mode, which turns off some internal circuits and extends the on time to achieve an ultra-low I_Q .

When the load increases, and the interval drops to be shorter than 6 μ s, the part exits sleep mode and enters AAM mode. In AAM mode, the device employs a zero-current detection (ZCD) circuit to turn off the LS-FET and prevent a negative I_L from flowing at light loads. The device exits AAM mode if the MODE pin goes high. If there is a fault (e.g. over-voltage (OV) or over-temperature (OT) faults) in sleep mode, the internal circuits are not disabled.

Frequency Spread Spectrum (FSS)

The MPQ4347/4347J uses a 12kHz modulation frequency with a 128-step triangular profile to spread the internal oscillator frequency across a 20% ($\pm 10\%$) window. The absolute frequency step size varies proportionally with f_{SW} to

maintain the $\pm 10\%$ frequency spread (see Figure 2).

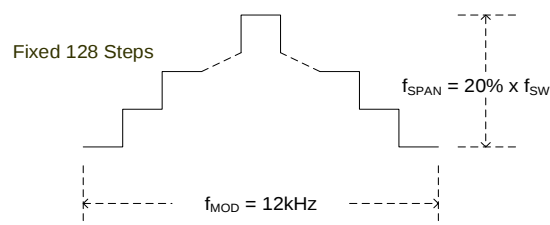


Figure 2: Spread Spectrum

Sidebands are created by modulating f_{SW} with the triangle modulation waveform. The emission power of the fundamental f_{SW} and its harmonics is distributed into smaller pieces. This significantly reduces EMI noise.

Low-Dropout (LDO) Mode

When V_{IN} drops to about 7V, the MPQ4347/4347J folds back the frequency. When V_{IN} is almost equal to V_{OUT} , the device enters low-dropout (LDO) mode. This allows for a shorter off time to achieve a higher duty cycle.

The effective duty cycle during the device's dropout period is mainly influenced by the voltage drops across the power MOSFET, the inductor resistance, the LS-FET diode, and the PCB resistance.

Start-Up and Shutdown

If both V_{IN} and EN exceed their respective thresholds, the device starts up. The reference block starts first, generating a stable reference voltage and currents, and then the internal regulator is enabled. The regulator provides a stable supply for the remaining circuitries.

While the internal supply rail is up, an internal timer holds the power MOSFET off for about 50 μ s to blank any start-up glitches. When the SS block is enabled, it first holds its SS output low to ensure that the remaining circuits are ready. Then the SS block slowly ramps up.

Three events can shut down the chip: EN going low, V_{IN} going low, and thermal shutdown. During the shutdown procedure, the signaling path is blocked first to avoid any fault triggering. Then V_{COMP} and the internal supply rail are pulled down. The floating driver is not subject to this shutdown command, but its charging path is disabled.

SYNCIN and SYNCO

f_{SW} can be synchronized to the rising edge of a clock signal applied to the SYNCIN/MODE pin. The recommended SYNCIN frequency range is between 90% and 115% of f_{SW} , which is set by an external frequency resistor.

The SYNCO pin can output a clock signal in phase with the internal oscillator signal (inverter to switching clock), or the external SYNCIN frequency.

Thermal Shutdown

Thermal shutdown is implemented to prevent the chip from thermal runaway. When the silicon die temperature exceeds its upper threshold (about 170°C), the power MOSFETs shut down. Once the temperature drops below its lower threshold (about 150°C), the thermal shutdown condition is removed, and the chip is starts up again and resumes normal operation.

APPLICATION INFORMATION

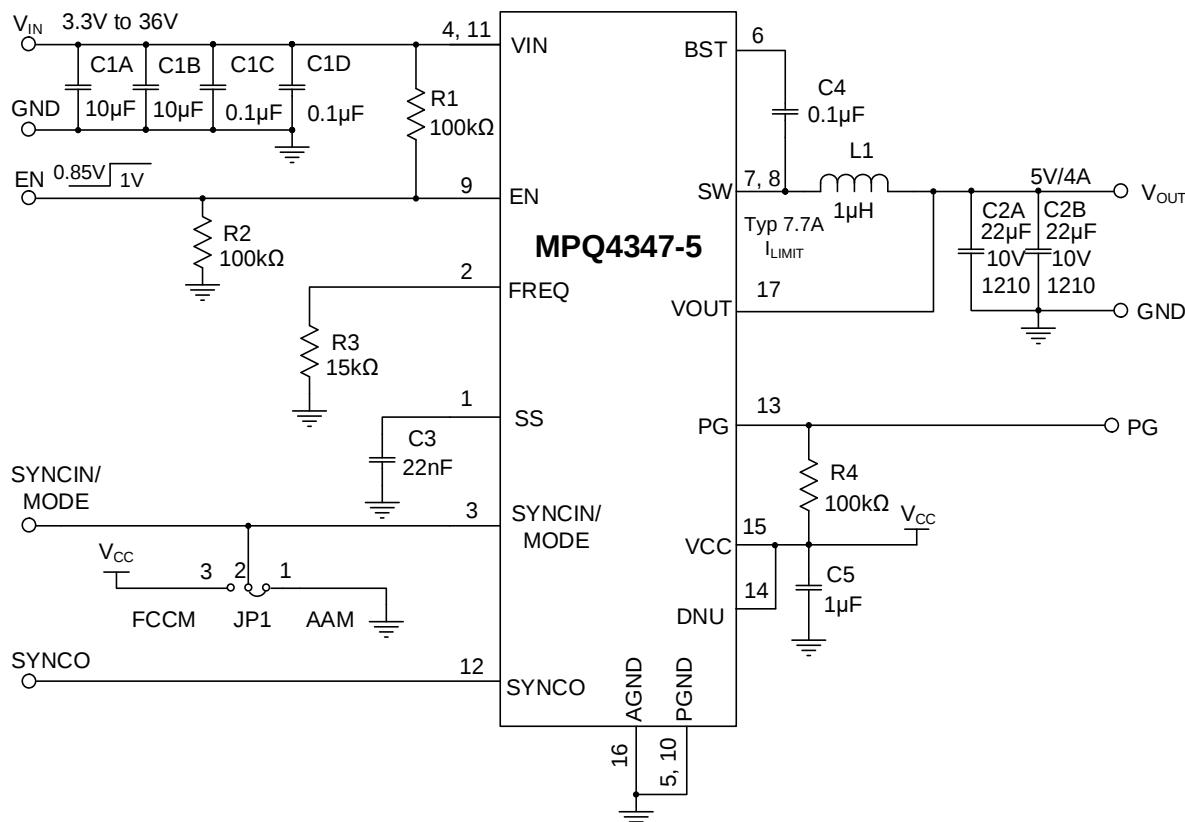


Figure 3: Typical Application Circuit for the MPQ4347GLE-5 ($V_{OUT} = 5V$, $f_{SW} = 2.2MHz$)

Table 1: Design Guide Index

Pin #	Pin Name	Component	Design Guide Index
1	SS	C3	Selecting the Soft-Start Capacitor (SS, Pin 1)
2	FREQ	R3	Setting the Switching Frequency (f_{sw}) (FREQ, Pin 2)
3	SYNCIN/MODE	-	SYNC Input and Mode Selection (SYNCIN/MODE, Pin 3)
4, 11	VIN	C1A, C1B, C1C, C1D	Selecting the Input Capacitors (VIN, Pins 4 and 11)
5, 10, 16	PGND	-	Connection to GND (GND, Pins 5, 10, and 16)
6	BST	C4	Bootstrap Charging (BST, Pin 6)
7, 8	SW	L1, C2A, C2B	Selecting the Inductor; Selecting the Output Capacitor (SW, Pins 7 and 8)
9	EN	R1, R2	Enable (EN, Pin 9) and V_{IN} Under-Voltage Lockout (UVLO)
12	SYNCO	-	SYNCO (Pin 12)
13	PG	R4	Power Good (PG) Indicator (PG, Pin 13)
14	DNU	-	DNU (Pin 14)
15	VCC	C5	Input Bias Supply (VCC, Pin 15)
17	VOUT	-	VOUT (Pin 17)

Selecting the Soft-Start Capacitor (SS, Pin 1)

Soft start (SS) is implemented to prevent the converter's V_{OUT} from overshooting during start-up.

When soft start begins, an internal current source begins charging the external soft-start capacitor (C_{SS}). When the soft-start voltage (V_{SS}) is below the internal reference voltage (V_{REF}), V_{SS} overrides V_{REF}, so the error amplifier (EA) uses V_{SS} as the reference. When V_{SS} exceeds V_{REF}, V_{REF} regains control.

C_{SS} can be calculated with Equation (1):

$$C_{SS}(\text{nF}) = \frac{t_{SS}(\text{ms}) \times I_{SS}(\mu\text{A})}{V_{REF}(\text{V})} = 16.6 \times t_{SS}(\text{ms}) \quad (1)$$

The SS pin can be used for tracking and sequencing.

Setting the Switching Frequency (f_{sw}) (FREQ, Pin 2)

f_{sw} can be configured by an external resistor connected from the FREQ pin to ground, placed as close to the device as possible.

The resistance that sets f_{sw} (R_{FREQ}/R3) can be selected using the f_{sw} vs. R_{FREQ} curves. Figure 4 shows the f_{sw} vs. R_{FREQ} curve when f_{sw} is between 1000kHz and 2500kHz.

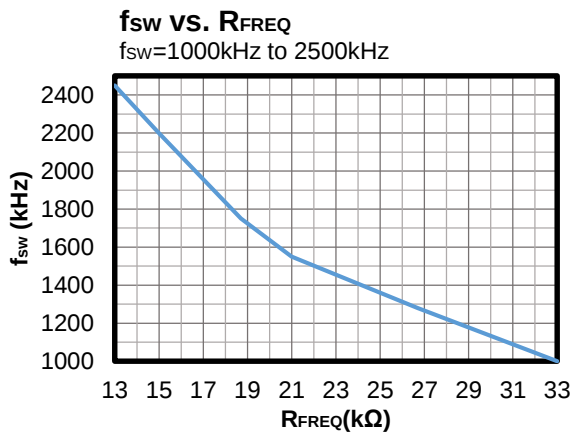


Figure 4: f_{sw} vs. R_{FREQ}

Figure 5 shows the f_{sw} vs. R_{FREQ} curve when f_{sw} is between 350kHz and 1000kHz.

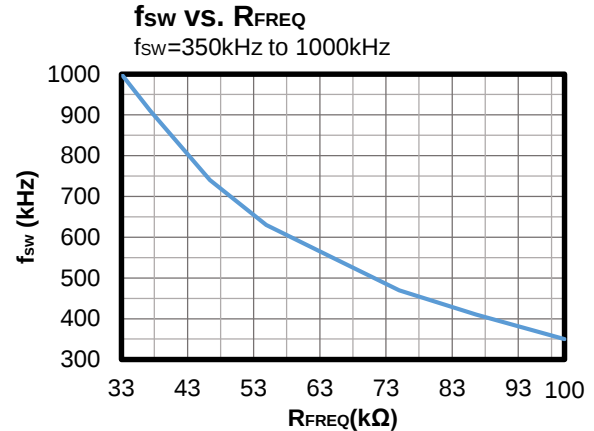


Figure 5: f_{sw} vs. R_{FREQ}

Table 2 shows some common f_{sw} and R_{FREQ} values when selecting f_{sw}.

Table 2: f_{sw} vs. R_{FREQ}

R _{FREQ} (kΩ)	f _{sw} (kHz)
100	350
86.6	410
75	470
64.9	550
54.9	630
46.4	740
37.4	910
33	1050
26.7	1280
21	1550
18.7	1750
15	2200
13	2450

SYNC Input and Mode Selection (SYNCIN/MODE, Pin 3)

When the SYNCIN/MODE pin is used as the SYNC input pin (SYNCIN), f_{sw} can be synchronized to the rising edge of a clock signal applied to the SYNCIN/MODE pin. The recommended SYNCIN frequency range is between 90% and 115% of f_{sw}.

When this pin is used for mode selection (MODE), pulling this pin high forces the device to operate in FCCM, while pulling it low forces the device to work in AAM mode (see Table 3).

Table 3: Mode Selection

SYNCIN/MODE Input	Operation
<0.4V	AAM mode
>1.8V	FCCM
External clock in	FCCM

Selecting the Input Capacitor (V_{IN}, Pins 4 and 11)

The step-down converter has a discontinuous input current, and requires a capacitor to supply AC current to the converter while maintaining the DC input voltage. For the best performance, use low-ESR capacitors. Ceramic capacitors with X5R or X7R dielectrics are highly recommended because of their low ESR and small temperature coefficients.

For most applications, it is recommended to use a 4.7μF to 10μF capacitor. It is strongly recommended to use another, lower-value capacitor (e.g. 0.1μF) with a small package size (0603) to absorb high-frequency switching noise. Place the smaller capacitor as close to V_{IN} and GND as possible.

Since the input capacitor (C_{IN}) absorbs the input switching current, it requires an adequate ripple current rating. The RMS current for C_{IN} can be estimated with Equation (2):

$$I_{CIN} = I_{LOAD} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)} \quad (2)$$

The worst-case condition occurs at V_{IN} = 2 × V_{OUT}, calculated with Equation (3):

$$I_{CIN} = \frac{I_{LOAD}}{2} \quad (3)$$

For simplification, choose an input capacitor with an RMS current rating greater than half of the maximum load current.

The input capacitor can be electrolytic, tantalum, or ceramic. When using electrolytic or tantalum capacitors, add a small, high-quality ceramic capacitor (e.g. 0.1μF) as close to the IC as possible. When using ceramic capacitors, ensure that they have enough capacitance to provide a sufficient charge to prevent an excessive voltage ripple at the input. The input voltage ripple (ΔV_{IN}) caused by the capacitance can be estimated with Equation (4):

$$\Delta V_{IN} = \frac{I_{LOAD}}{f_{SW} \times C_{IN}} \times \frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (4)$$

Input Voltage (V_{IN}) Over-Voltage Protection (OVP)

The MPQ4347/4347J has a built-in V_{IN} over-voltage protection (OVP) circuit. V_{IN} OVP becomes active at 25V. When V_{IN} exceeds the OVP threshold (typically 38V), the LS-FET turns on until the inductor current (I_L) is fully discharged, and then switching stops. When V_{IN} drops to the OV falling threshold (typically 28V), and the hiccup restart delay time expires, the device completes a soft-start cycle and resumes normal regulation.

Bootstrap Charging (BST, Pin 6)

The BST capacitor (C₄) is recommended to be between 0.1μF and 0.22μF.

It is not recommended to place a resistor (R_{BST}) in series with the BST capacitor unless there is a strict EMI requirement. R_{BST} helps enhance EMI performance and reduce voltage stress at high input voltages, but it also increases power consumption and reduces efficiency. When R_{BOOT} is necessary, it should be below 10Ω.

The bootstrap capacitor (C_{BST}) is charged and regulated to about 5V by the dedicated internal bootstrap regulator. When the voltage between the BST and SW nodes is below its regulation voltage, an N-channel MOSFET pass transistor connected from V_{CC} to BST turns on to charge the bootstrap capacitor. The external circuit should provide enough voltage headroom to facilitate charging.

When the HS-FET is on, the BST voltage exceeds V_{CC}, so the bootstrap capacitor cannot be charged.

At higher duty cycles, the time available for bootstrap charging is shorter, so the bootstrap capacitor may not be sufficiently charged. If the external circuit has an insufficient voltage and not enough time to charge the bootstrap capacitor, use additional external circuitry to ensure that the bootstrap voltage remains within the normal operation range.

Selecting the Output Capacitor (SW, Pins 7 and 8)

The output capacitor maintains the DC output voltage. Use ceramic, tantalum, or low-ESR electrolytic capacitors. For the best results, use

low-ESR capacitors to keep the output voltage ripple low.

The output voltage ripple (ΔV_{OUT}) can be estimated with Equation (5):

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_{SW} \times L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times \left(R_{ESR} + \frac{1}{8f_{SW} \times C_{OUT}}\right) \quad (5)$$

Where L is the inductance, and R_{ESR} is the equivalent series resistance (ESR) value of the output capacitor.

For ceramic capacitors, the capacitance dominates the impedance at the switching frequency and causes the majority of the output voltage ripple. For simplification, the output voltage ripple (ΔV_{OUT}) can be estimated with Equation (6):

$$\Delta V_{OUT} = \frac{V_{OUT}}{8 \times f_{SW}^2 \times L \times C_{OUT}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (6)$$

For tantalum or electrolytic capacitors, the ESR dominates the impedance at the switching frequency. For simplification, the output voltage ripple (ΔV_{OUT}) can be estimated with Equation (7):

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_{SW} \times L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times R_{ESR} \quad (7)$$

The characteristics of the output capacitor also affect the stability of the regulation system. The part can be optimized for a wide range of capacitances and ESR values.

Selecting the Inductor

A 1 μ H to 10 μ H inductor with a DC current rating at least 25% greater than the maximum load current is recommended for most applications. For higher efficiency, choose an inductor with a lower DC resistance. A larger-value inductor results in less ripple current and a lower output ripple voltage, but also has a larger physical size, higher series resistance, and lower saturation current. A good rule for determining the inductance is to allow the inductor ripple current to be approximately 30% of the maximum load current. The inductance (L) can be calculated with Equation (8):

$$L = \frac{V_{OUT}}{f_{SW} \times \Delta I_L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (8)$$

Where ΔI_L is the peak-to-peak inductor ripple current.

Choose the inductor ripple current to be approximately 30% of the maximum load current. The maximum peak inductor current (I_{LP}) can be calculated with Equation (9):

$$I_{LP} = I_{LOAD} + \frac{V_{OUT}}{2f_{SW} \times L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (9)$$

Peak and Valley Current Limit

Both the HS-FET and LS-FET have cycle-by-cycle current-limit protection. When I_L reaches the high-side peak current limit (typically 7.7A) or the rising edge of the internal clock is reached while the current is rising and the HS-FET is on, the HS-FET is forced off immediately to prevent the current from rising further. When the LS-FET is on, the valley current limit circuit blocks the PWM from turning on the HS-FET until I_L is below the low-side valley current limit (typically 5.9A). This current limit scheme prevents current runaway if an overload or short-circuit event occurs.

Short-Circuit Protection (SCP)

If the output is shorted to ground, V_{OUT} drops below 70% of its nominal output, and the LS-FET current exceeds the valley current limit (5.9A), the device turns on the LS-FET until I_L is fully discharged. The device also begins slowly discharging C_{SS} . The device restarts with a full soft start when C_{SS} is fully discharged. This hiccup process repeats until the fault is removed.

Output Over-Voltage Protection (OVP) and Discharge

There is an internal V_{OUT} OVP circuit. When the device is operating in discontinuous conduction mode (DCM) and V_{OUT} exceeds 106% of the set V_{OUT} , an output discharge path from V_{OUT} to GND is activated to discharge V_{OUT} . The output discharge path remains activated until V_{OUT} returns to its regulated value, and switching resumes.

When the part is operating in FCCM and V_{OUT} exceeds 106% of the set V_{OUT} , the output discharge path turns on. If the negative current limit is triggered 265 times, the part enters hiccup mode and switching stops. Once V_{OUT} drops to 105% of the set V_{OUT} , a new SS cycle begins. The V_{OUT} discharge path remains on until V_{OUT}

reaches is regulated value, and then the part begins switching.

Enable (EN, Pin 9) and V_{IN} Under-Voltage Lockout (UVLO)

The EN pin is a digital control pin that turns the device on and off.

Enabled by External Logic High/Low Signal

When the EN voltage is about 0.7V, the VCC supply turns on. When V_{IN} exceeds 2.7V, it then provides an accurate reference voltage for EN threshold. Forcing EN above its rising threshold voltage (1V) turns on the device. Driving EN below 0.85V turns off the device.

Configurable V_{IN} Under-Voltage Lockout (UVLO)

When V_{IN} is sufficiently high, the chip can be enabled and disabled via the EN pin. An internal pull-down resistor in this circuit can generate a configurable V_{IN} under-voltage lockout (UVLO) threshold and hysteresis through the EN pin.

The part requires a higher voltage ($\geq 3.3V$) for V_{IN} to directly start up the device. The part has an internal, fixed UVLO threshold. The rising threshold is 3V, while the falling threshold is about 2.8V. For applications that require a higher UVLO point, an external resistor divider placed between V_{IN} and EN can raise the equivalent UVLO threshold (see Figure 6).

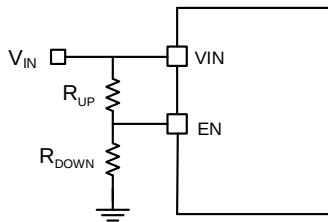


Figure 6: Adjustable UVLO Using EN Divider

The UVLO rising and falling thresholds can be calculated with Equation (10) and Equation (11), respectively:

$$V_{IN_UVLO_RISING} = \left(1 + \frac{R_{UP}}{R_{DOWN}}\right) \times V_{EN_RISING} \quad (10)$$

$$V_{IN_UVLO_FALLING} = \left(1 + \frac{R_{UP}}{R_{DOWN}}\right) \times V_{EN_FALLING} \quad (11)$$

Where V_{EN_RISING} is 1V, and V_{EN_FALLING} is 0.85V.

SYNCO (Pin 12)

The SYNCO pin outputs a clock signal in phase with the internal oscillator signal or the external SYNCIN clock. Float the SYNCO pin if it is not used.

PG (Pin 13)

The MPQ4347/4347J includes an open-drain power good (PG) output that indicates whether the regulator's output is within its nominal range. PG goes high if V_{OUT} is within 94% to 106% of its nominal voltage; PG goes low if V_{OUT} is above 107% or below 93% of its nominal voltage. Float PG if it is not used. The PG resistance (R_{PG}/ R4) is recommended to be about 100kΩ.

DNU (Pin 14)

Connect the DNU pin directly to the VCC pin.

Setting the VCC Capacitor (VCC, Pin 15)

Most of the internal circuitry is powered by the internal, 5V VCC regulator. This regulator uses V_{IN} as its input and operates across the full V_{IN} range. When V_{IN} exceeds 5V, V_{CC} is in full regulation. When V_{IN} is below 5V, the output V_{CC} degrades.

The VCC capacitor should have a capacitance at least 10 times greater than the boost capacitor, and at least 1μF nominally. A VCC capacitor with a nominal value exceeding 68μF is not recommended.

VOUT (Pin 17)

Because the feedback resistor divider is integrated internally, connect the VOUT pin directly to the output (Figure 7).

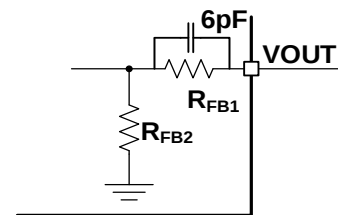


Figure 7: Feedback Divider Network for Fixed Output Version

The selectable fixed-output options are as follows: 1V, 1.1V, 1.8V, 2.5V, 3V, 3.3V, 3.7V, 3.8V, and 5V.

Table 4 on page 45 shows the relationship between the internal R_{FBX} values and V_{OUT}.

Table 4: R_{FBx} vs. V_{OUT}

V _{OUT} (V)	R _{FB1} (MΩ)	R _{FB2} (MΩ)
1	1.33	2
1.1	1.67	2
1.8	4	2
2.5	6.33	2
3	8	2
3.3	9	2
3.7	10.33	2
3.8	10.67	2
5	14.67	2

Connection to GND (GND, Pins 5, 10, and 16)

See the PCB Layout Guidelines section below for more details.

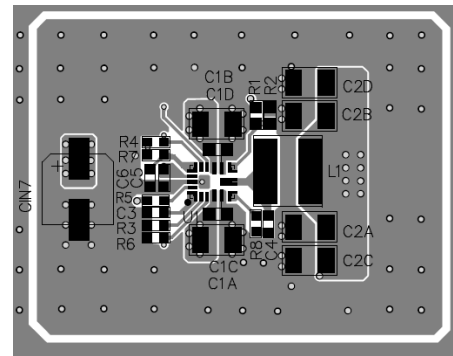
PCB Layout Guidelines ⁽¹²⁾

Efficient PCB layout, especially input capacitor placement, is critical for stable operation. A 4-layer layout is strongly recommended to improve thermal performance. For the best results, refer to Figure 8 and follow the guidelines below:

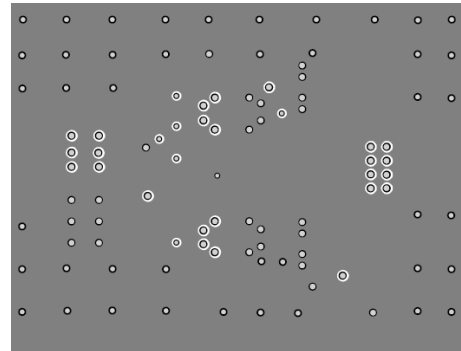
1. Place the symmetric input capacitors as close to VIN and GND as possible.
2. Use a large ground plane to connect directly to PGND.
3. Add vias near PGND if the bottom layer is a ground plane.
4. Ensure that the high-current paths at GND and VIN have short, direct, and wide traces.
5. Place the ceramic input capacitor, especially the small package size (0603) input bypass capacitor, as close to VIN and PGND as possible to minimize high-frequency noise.
6. Keep the connection of the input capacitor and VIN as short and wide as possible.
7. Place the VCC capacitor as close to VCC and GND as possible.
8. Route SW and BST away from sensitive analog areas, such as VOUT.
9. Use multiple vias to connect the power planes to the internal layers.

Note:

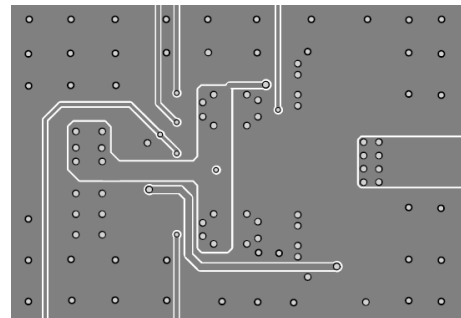
12) The recommended PCB layout is based on Figure 9 on page 46.



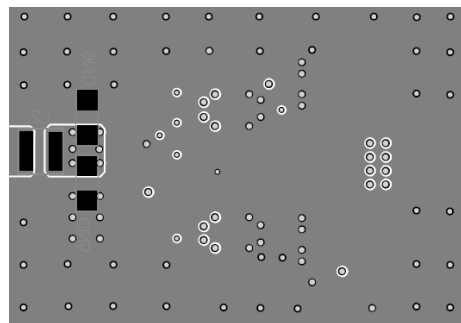
Top Layer



Mid-Layer 1



Mid-Layer 2



Bottom Layer

Figure 8: Recommended PCB Layout

TYPICAL APPLICATION CIRCUITS

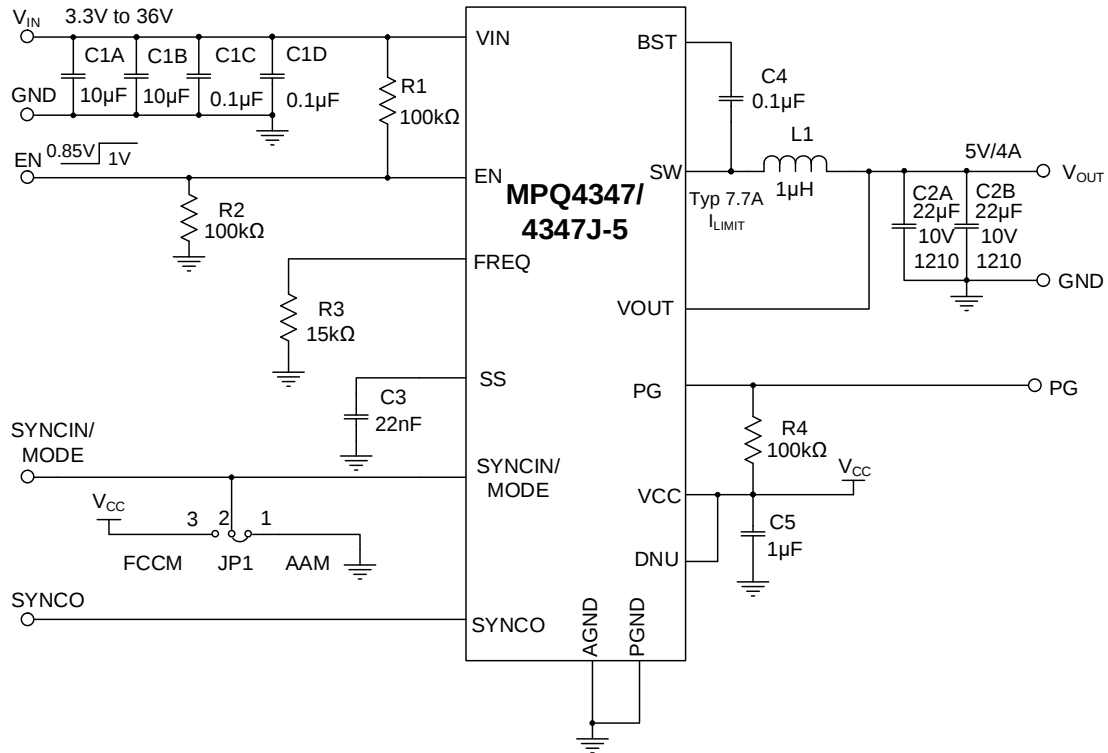


Figure 9: Typical Application Circuit ($V_{OUT} = 5V$, $f_{sw} = 2.2MHz$)

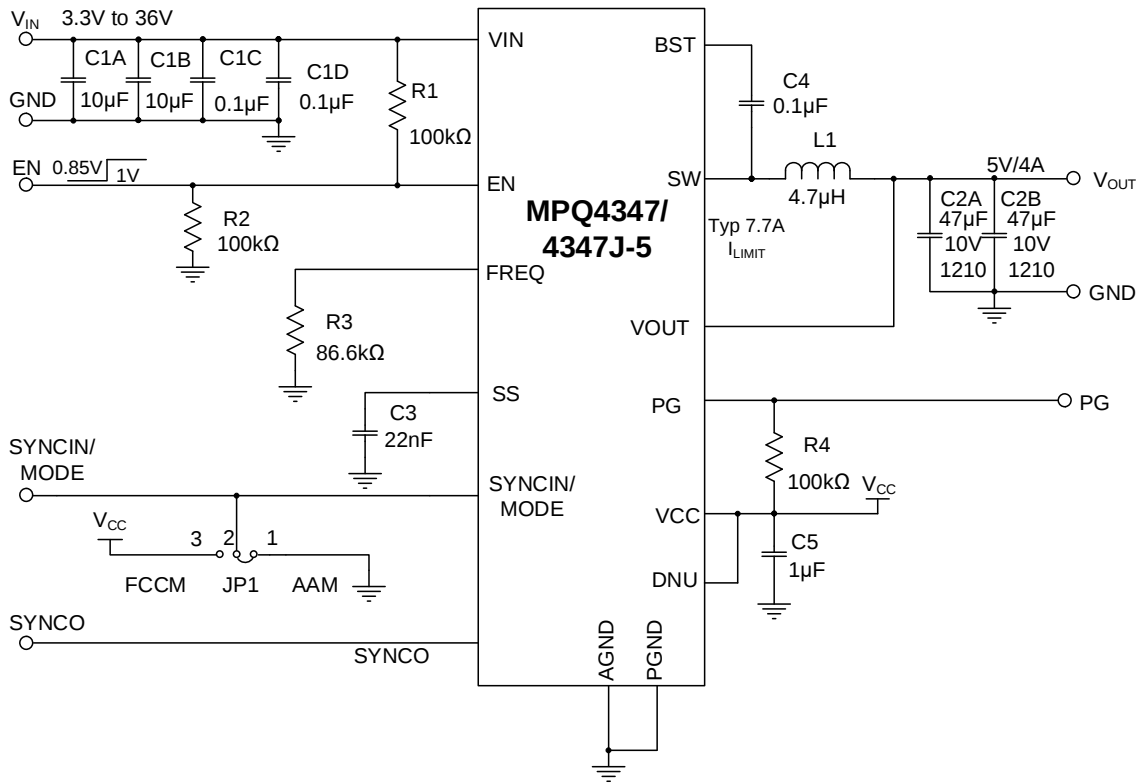


Figure 10: Typical Application Circuit ($V_{OUT} = 5V$, $f_{sw} = 410kHz$)

TYPICAL APPLICATION CIRCUITS (continued)

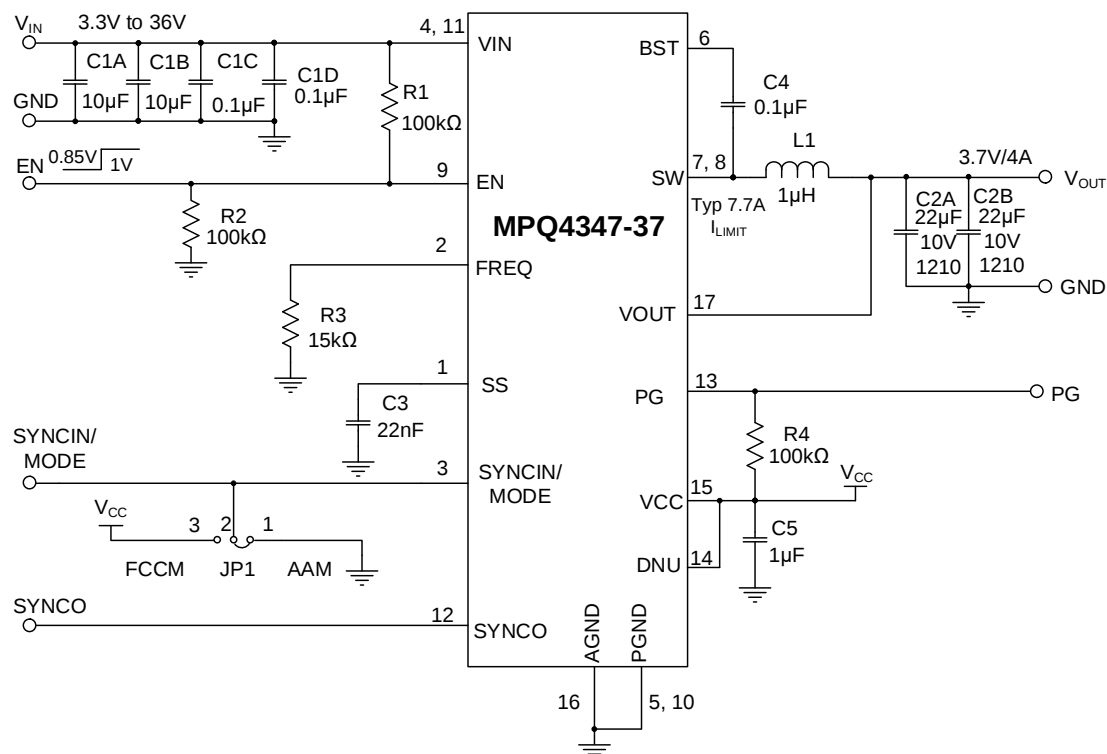


Figure 11: Typical Application Circuit ($V_{OUT} = 3.7V$, $f_{SW} = 2.2MHz$)

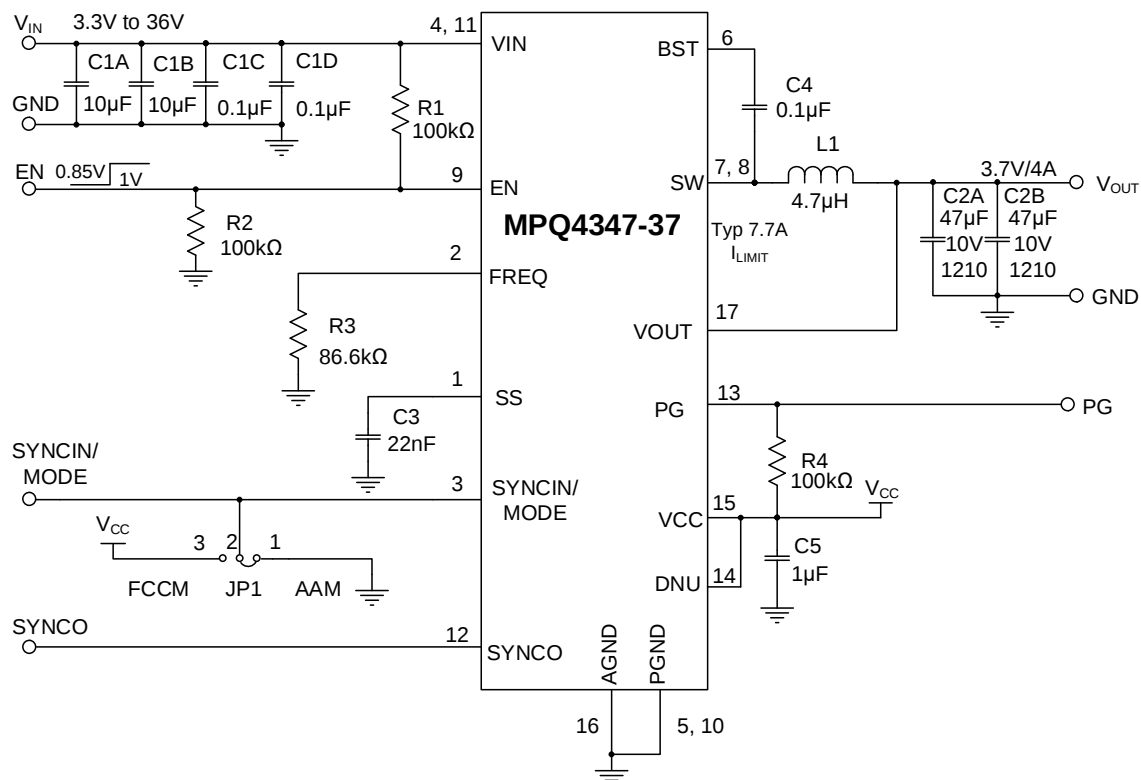


Figure 12: Typical Application Circuit ($V_{OUT} = 3.7V$, $f_{SW} = 410kHz$)

TYPICAL APPLICATION CIRCUITS *(continued)*

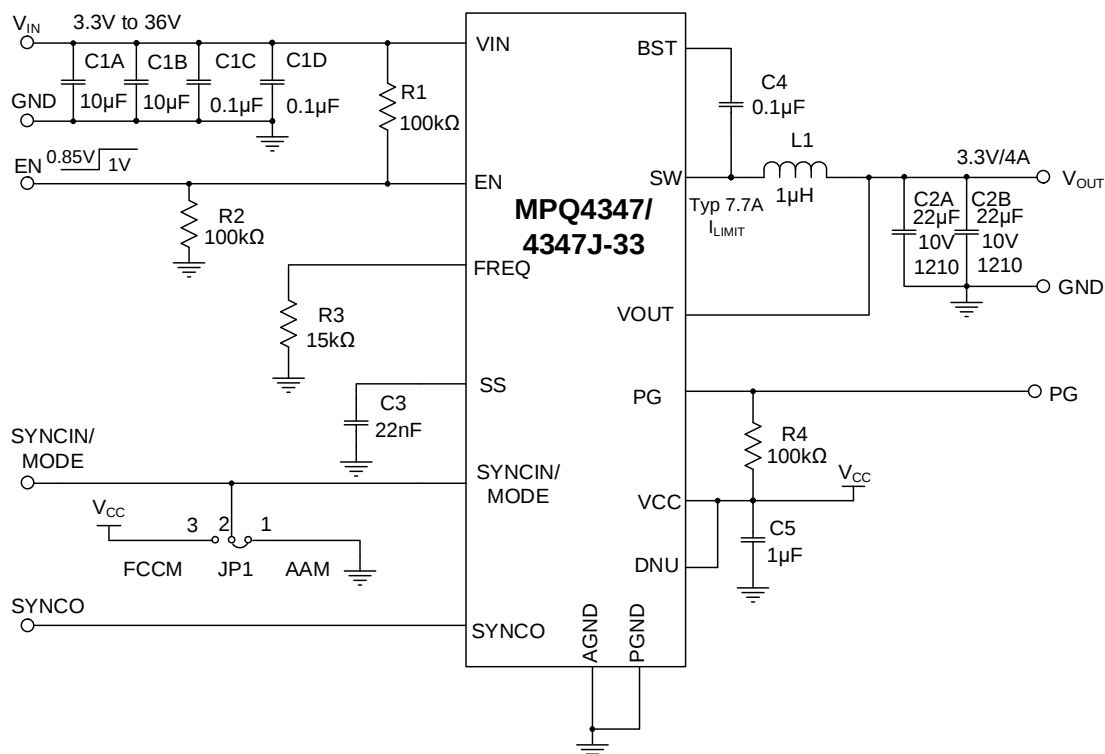


Figure 13: Typical Application Circuit ($V_{OUT} = 3.3V$, $f_{SW} = 2.2MHz$)

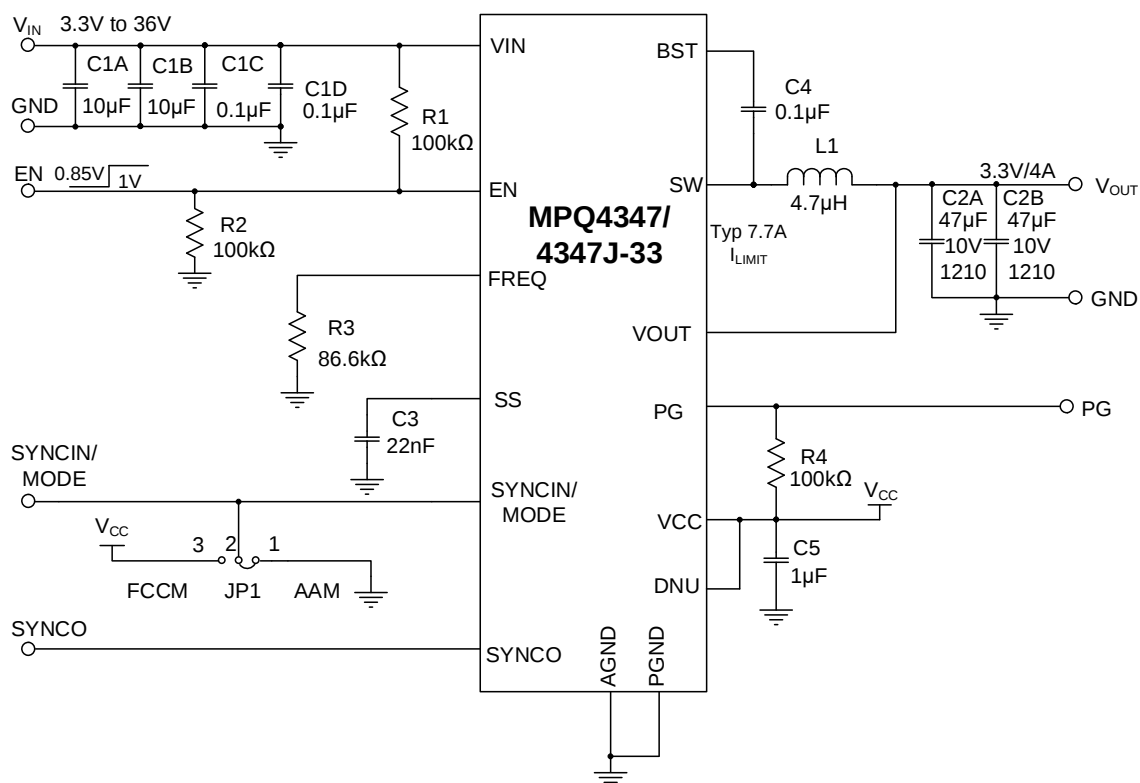


Figure 14: Typical Application Circuit ($V_{OUT} = 3.3V$, $f_{SW} = 410kHz$)

TYPICAL APPLICATION CIRCUITS *(continued)*

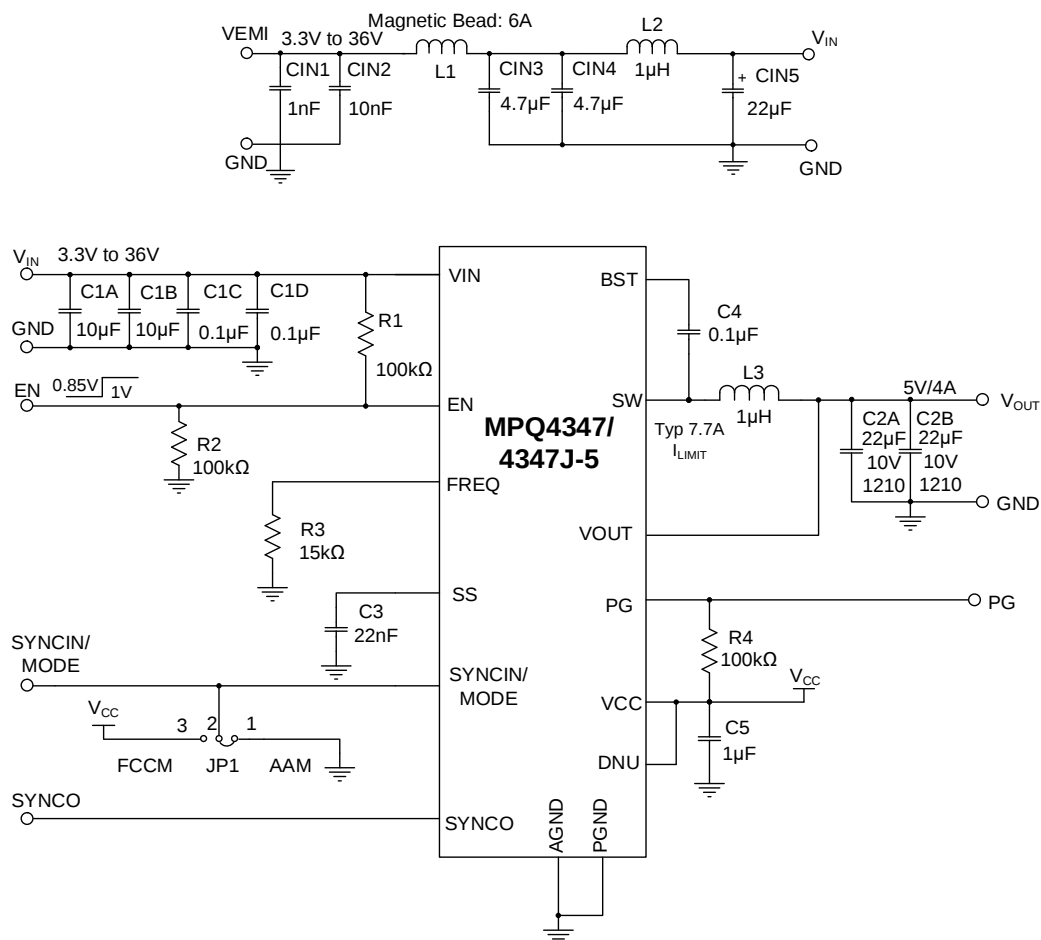


Figure 15: Typical Application Circuit ($V_{OUT} = 5V$, $f_{SW} = 2.2MHz$ with EMI Filter)

TYPICAL APPLICATION CIRCUITS *(continued)*

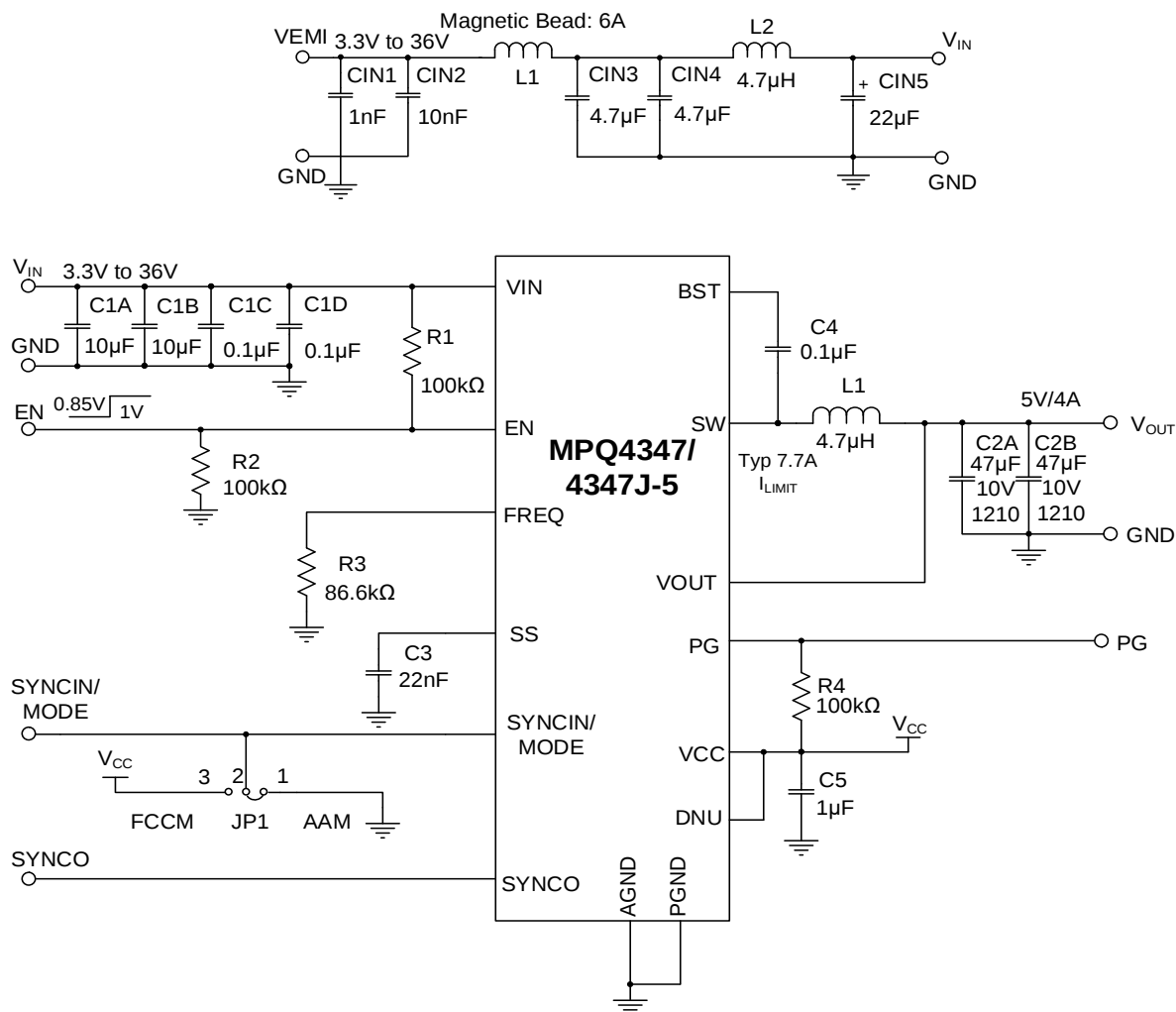
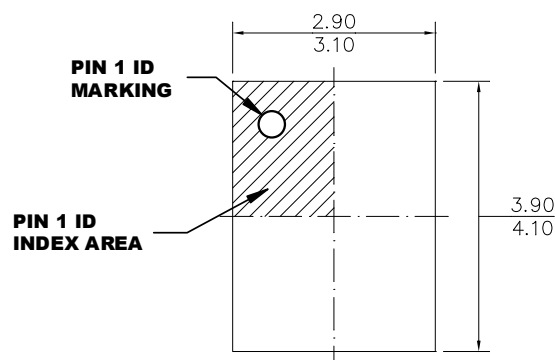


Figure 16: Typical Application Circuit ($V_{OUT} = 5V$, $f_{SW} = 410kHz$ with EMI Filter)

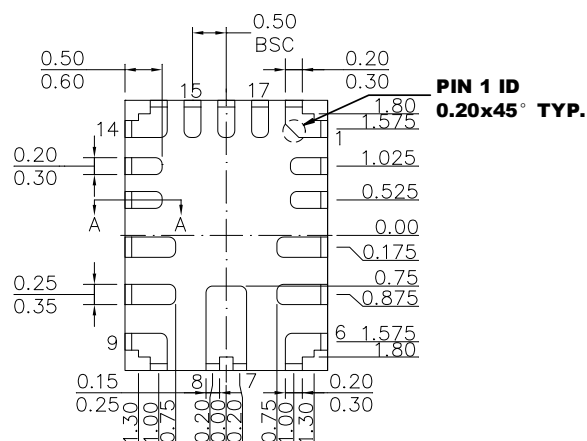
PACKAGE INFORMATION

QFN-17 (3mmx4mm)

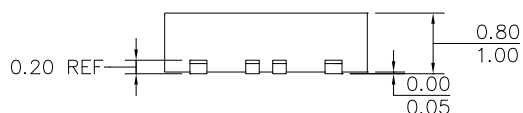
Wettable Flank



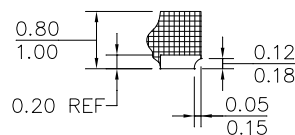
TOP VIEW



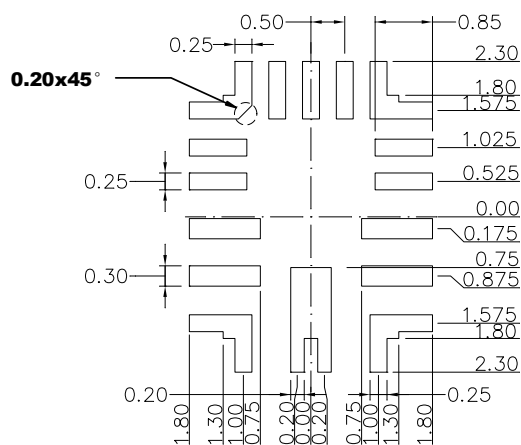
BOTTOM VIEW



SIDE VIEW



SECTION A-A



RECOMMENDED LAND PATTERN

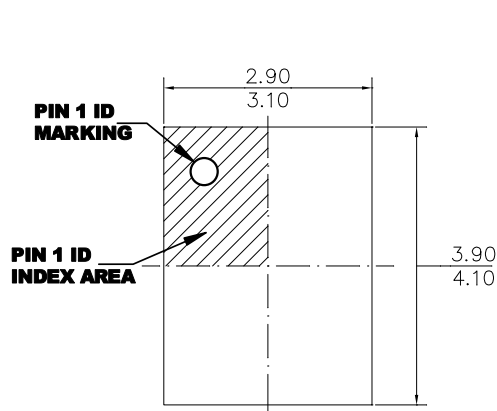
NOTE:

- 1) THE LEAD SIDE IS WETTABLE.
- 2) ALL DIMENSIONS ARE IN MILLIMETERS.
- 3) LEAD COPLANARITY SHALL BE 0.08 MILLIMETERS MAX.
- 4) JEDEC REFERENCE IS MO-220.
- 5) DRAWING IS NOT TO SCALE.

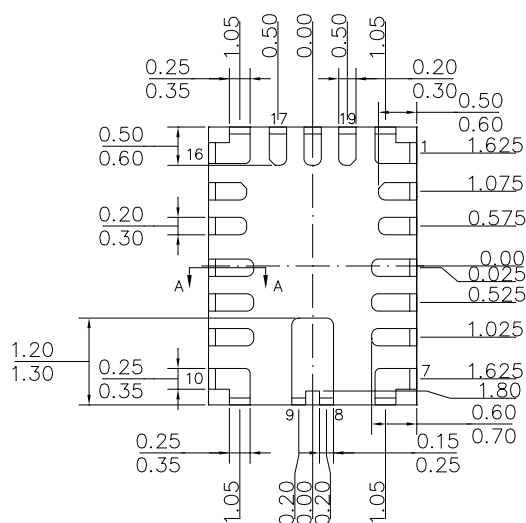
PACKAGE INFORMATION (continued)

QFN-19 (3mmx4mm)

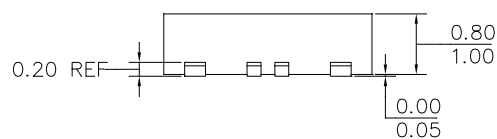
Wettable Flank



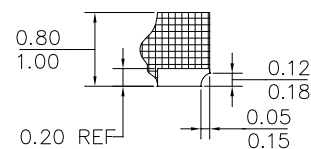
TOP VIEW



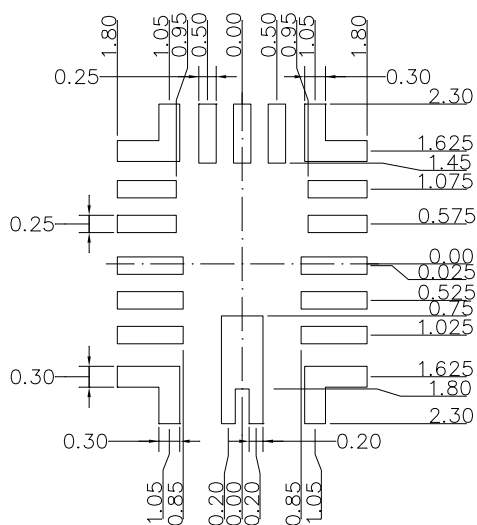
BOTTOM VIEW



SIDE VIEW



SECTION A-A

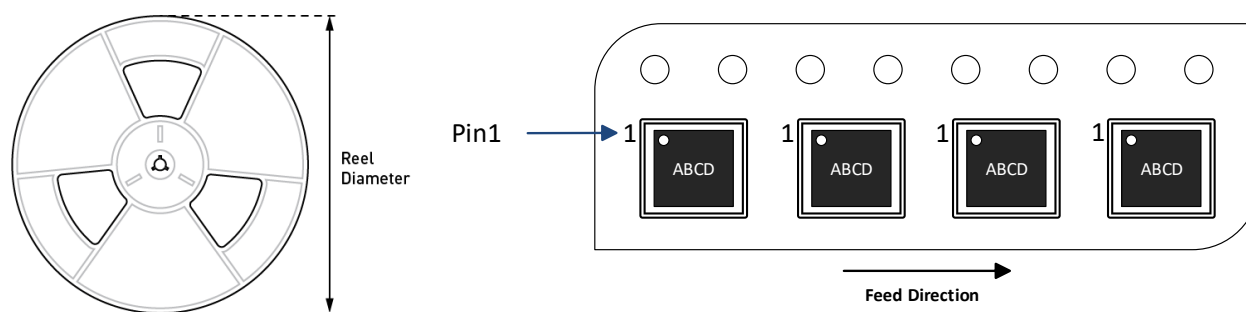


RECOMMENDED LAND PATTERN

NOTE:

- 1) THE LEAD SIDE IS WETTABLE.
- 2) ALL DIMENSIONS ARE IN MILLIMETERS.
- 3) LEAD COPLANARITY SHALL BE 0.08 MILLIMETERS MAX.
- 4) JEDEC REFERENCE IS MO-220.
- 5) DRAWING IS NOT TO SCALE.

CARRIER INFORMATION



Part Number	Package Description	Quantity/ Reel	Quantity/ Tube ⁽¹³⁾	Quantity/ Tray ⁽¹³⁾	Reel Diameter	Carrier Tape Width	Carrier Tape Pitch
MPQ4347GLE-33-AEC1-Z	QFN-17 (3mmx4mm)	5000	N/A	N/A	13in	12mm	8mm
MPQ4347GLE-37-AEC1-Z	QFN-17 (3mmx4mm)	5000	N/A	N/A	13in	12mm	8mm
MPQ4347GLE-5-AEC1-Z	QFN-17 (3mmx4mm)	5000	N/A	N/A	13in	12mm	8mm
MPQ4347JGLE-33-AEC1-Z	QFN-19 (3mmx4mm)	5000	N/A	N/A	13in	12mm	8mm
MPQ4347JGLE-5-AEC1-Z	QFN-19 (3mmx4mm)	5000	N/A	N/A	13in	12mm	8mm

Note:

13) N/A indicates “not available” in tubes. For 500 piece tape & reel prototype quantities, see factory. (Order code for 500 piece partial reel is “-P”, tape & reel dimensions same as full reel.)

REVISION HISTORY

Revision #	Revision Date	Description	Pages Updated
1.0	10/27/2022	Initial Release	-

Notice: The information in this document is subject to change without notice. Please contact MPS for current specifications. Users should warrant and guarantee that third-party Intellectual Property rights are not infringed upon when integrating MPS products into any application. MPS will not assume any legal responsibility for any said applications.